

WP 2 Process Development

Dr.-Ing. Christian Freitag, University of Stuttgart

Work Package 2

- HIPERDIAS application areas:
 - 3D Silicon processing
 - Fine cutting of metals
 - Diamond ablation
- Agenda:
 - Task 2.1: Fundamentals Si Processing
 - Task 2.2: Fundamentals Fine Cutting of Metals
 - Task 2.3: Fundamentals Diamond Ablation
 - Task 2.4: Upscaling

Partners involved:



BOSCH



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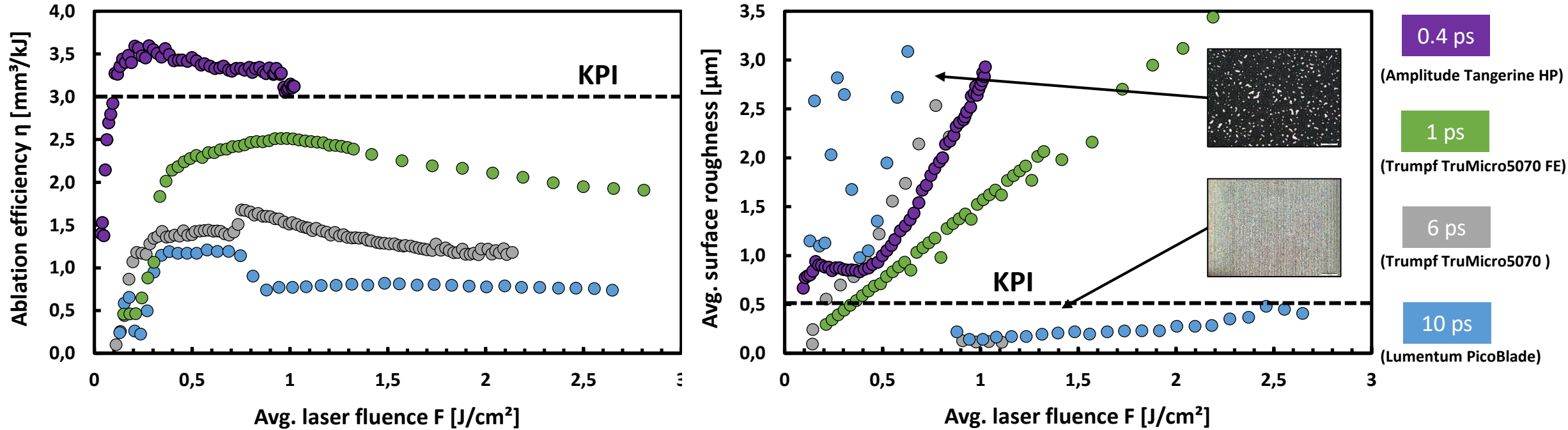
Partners involved:



BOSCH



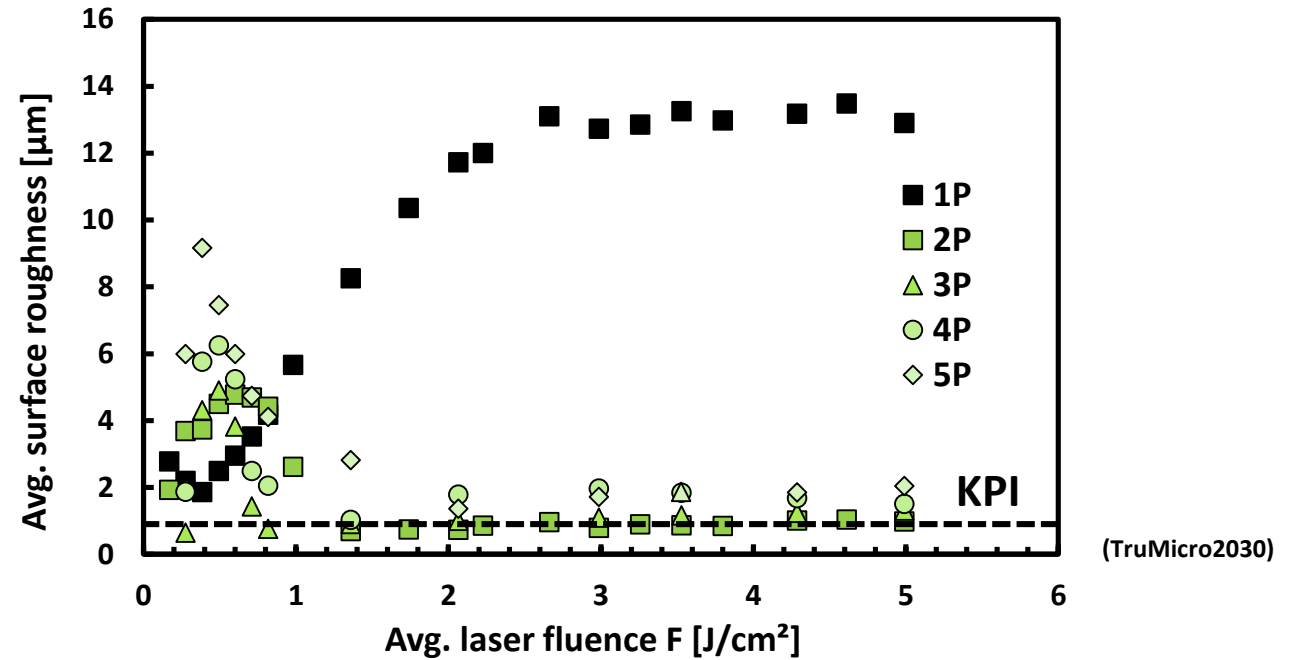
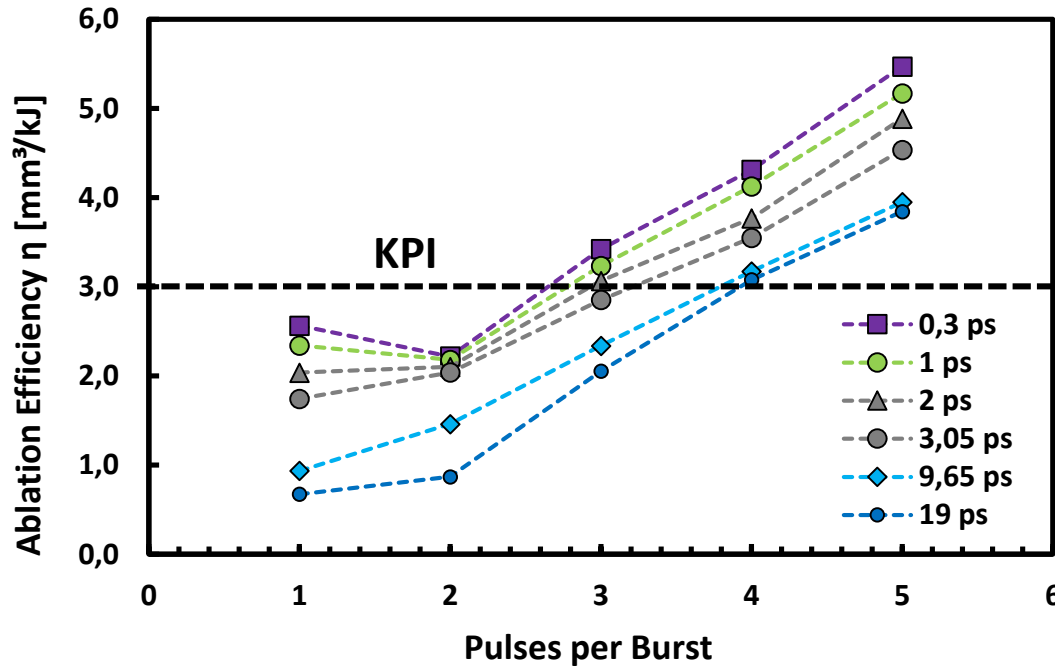
Task 2.1: Fundamental process development 3D Si processing



- Decisive KPI's (s. WP1): **ablation efficiency*** and **surface roughness**
- Parameters w/ highest impact: Avg. laser fluence and laser pulse duration
- Shift between ablation regimes observed for long pulse duration (> 1 ps): Jump in ablation efficiency, substantial decrease of surface roughness
- **Critical: trade-off between surface quality and productivity**

* Also referred as "energy specific ablation rate"

Task 2.1: Vital Parameter: Burst Mode



(TruMicro2030)

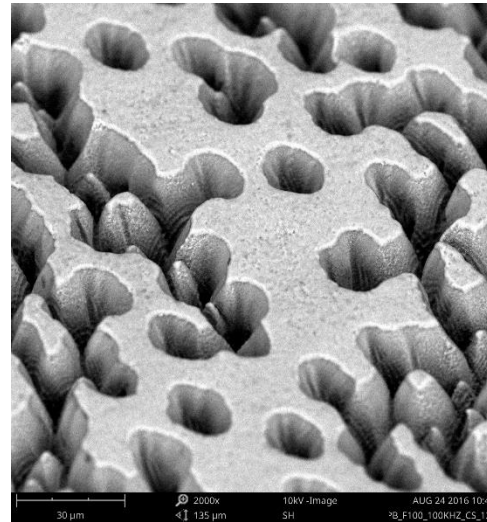
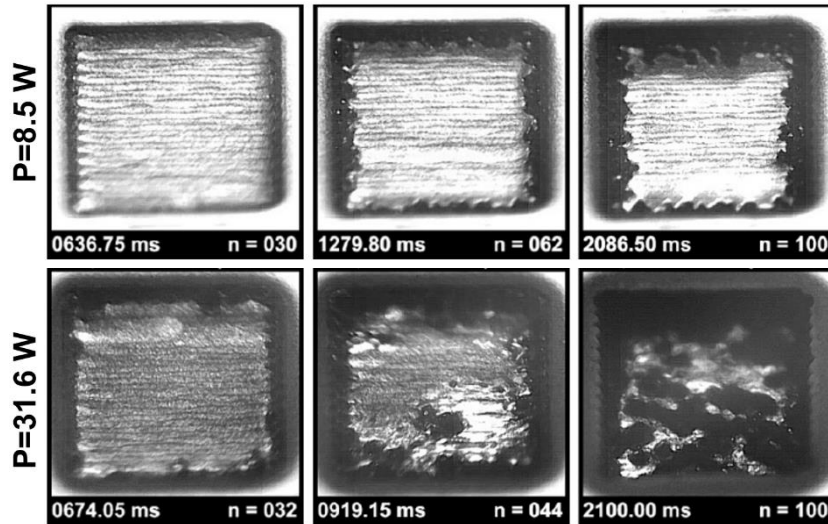
- Access to high quality regime at short pulse durations enabled! → *Tradeoff manageable*
- **Unexpected result:** Ablation efficiency can be increased with more pulses per burst

„Sweet spot“ identified w/ 5-pulse bursts, 0.3 ps pulse duration and 2 J/cm² fluence

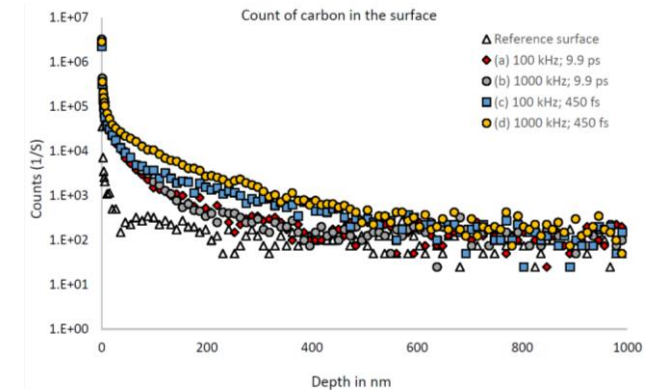
Task 2.1: Surface Condition

Deterioration of surface:

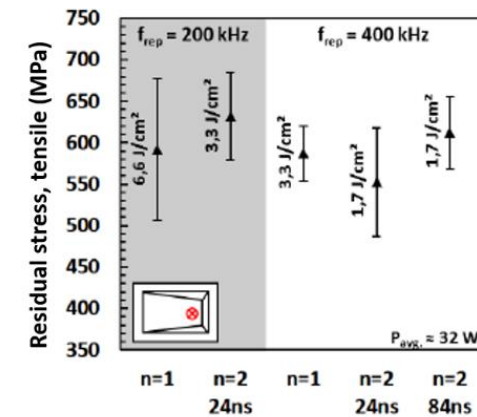
- High-Speed imaging, SEM analysis
- **Heat accumulation** leads to surface deterioration



Depth of damage layer (smooth surface) < 1 μm evaluated using SIMS*



Raman spectroscopy reveals high tensile residual stress in surface layer

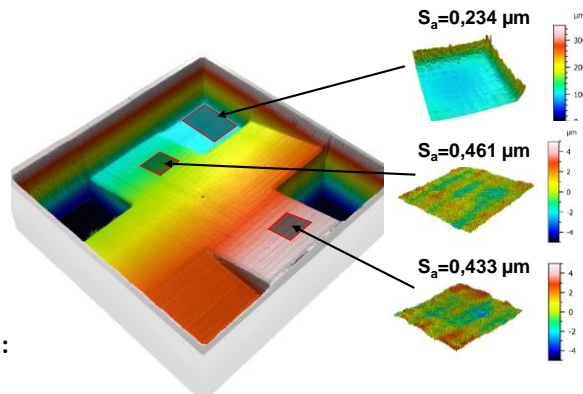
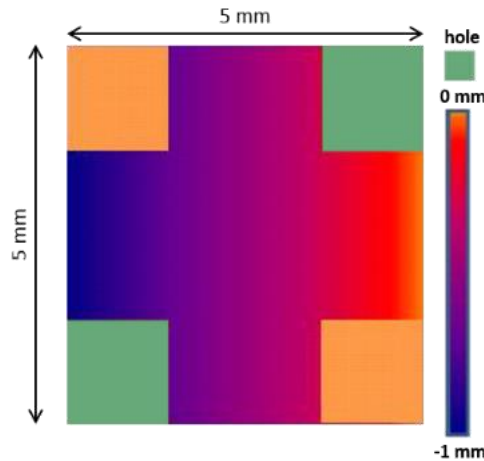


* Secondary Ion Mass Spectroscopy

Task 2.1: Status of BOSCH Key Performance Indicators

Test structure

- Features typical of potential applications:
- Ablated volume: 12 mm³
- Chamfer
- Steep walls
- Tight radius



KPI evaluation

Type	Unit	Target	Status M2017
Average ablation rate	mm ³ /s	≥1	0.05 → Upscaling (T2.4)
Peak ablation rate	mm ³ /s	≥3	0.1
Average ablation rate (specific)	mm ³ /kJ	≥1	3.1
Peak ablation rate (specific)	mm ³ /kJ	≥3	5.5
Shape deviation	μm	≤10	12.2
Average surface roughness Ra	μm	≤1	0.5
Surface damage thickness	μm	≤1	less than Ra
Surface defects > 1 μm	1/mm ²	none	0.05
Min. edge radius	μm	≤ 200	60
Max. edge-steepness	degree	≥ 70	82

- Results achieved: All KPIs w/i specifications, except for absolute ablation rate
- Translation of requirements into machine parameters → Discussion & comittment of Partners
- **Productivity/quality trade-off managed by using burst mode**

Bosch contribution including material from:

[D. Brinkmeier, Master's thesis]

[A. Hoppmann, Master's thesis]

[Y. Kasinathan, Master's thesis]

[B. Giese, Bachelor's thesis]

(performed @ Bosch Renningen)

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 - **Task 2.2: Fundamentals Fine Cutting of Metals**
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 - Task 2.4: Upscaling

Partners involved:



BOSCH



Task 2.2: Process limits fine cutting of metals

- Objectives:

 - Fundamental process development

 - Investigate ablation mechanism

 - Influence of processing parameters

 - Generate input for upscaling

Task 2.2: Process limits fine cutting of metals

- Objectives:

- Fundamental process development**

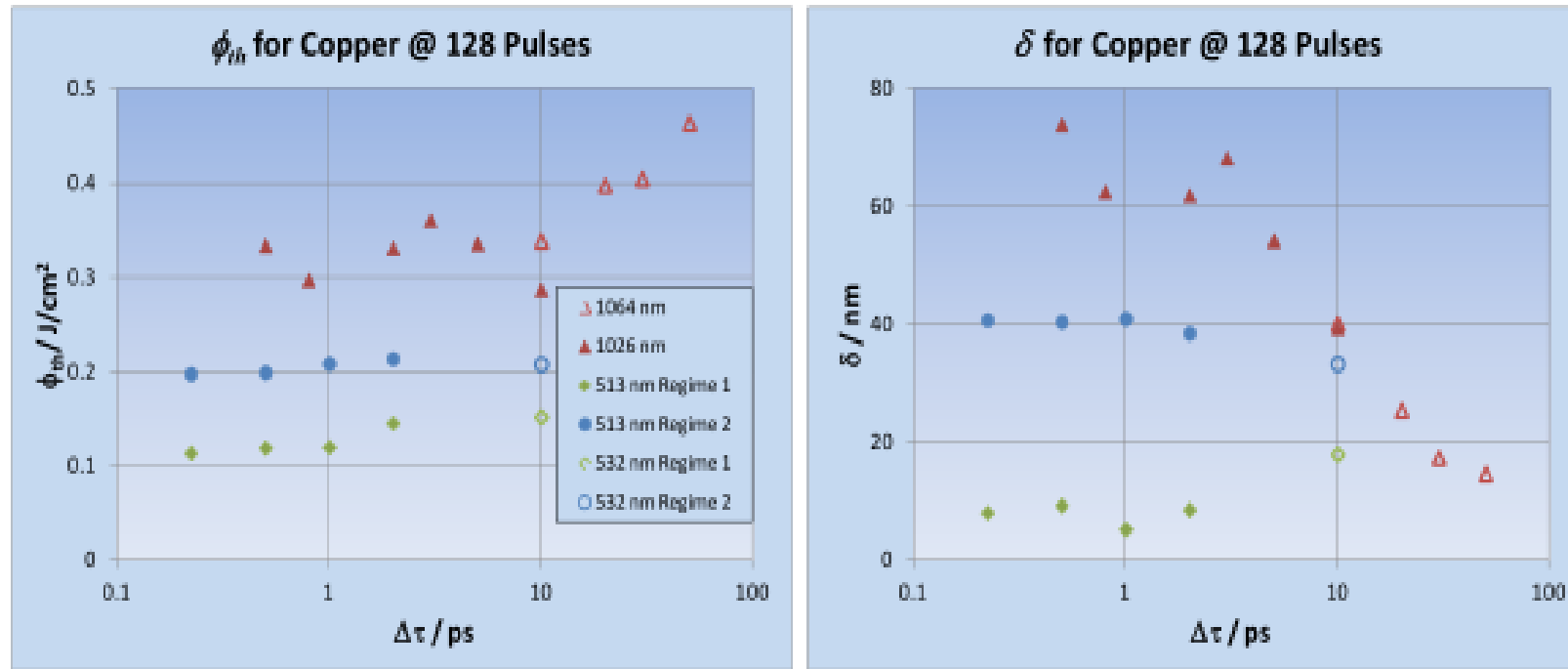
- Investigate ablation mechanism

- Influence of processing parameters

- Generate input for upscaling

Task 2.2: Process limits fine cutting of metals

- Literature review: **summary**



Results from Neuenschwander et al. demonstrating an unchanged threshold fluence below 10ps, and an increasing energy penetration depth below 10ps pulse duration.

Task 2.2: Process limits fine cutting of metals

- Objectives:

Fundamental process development

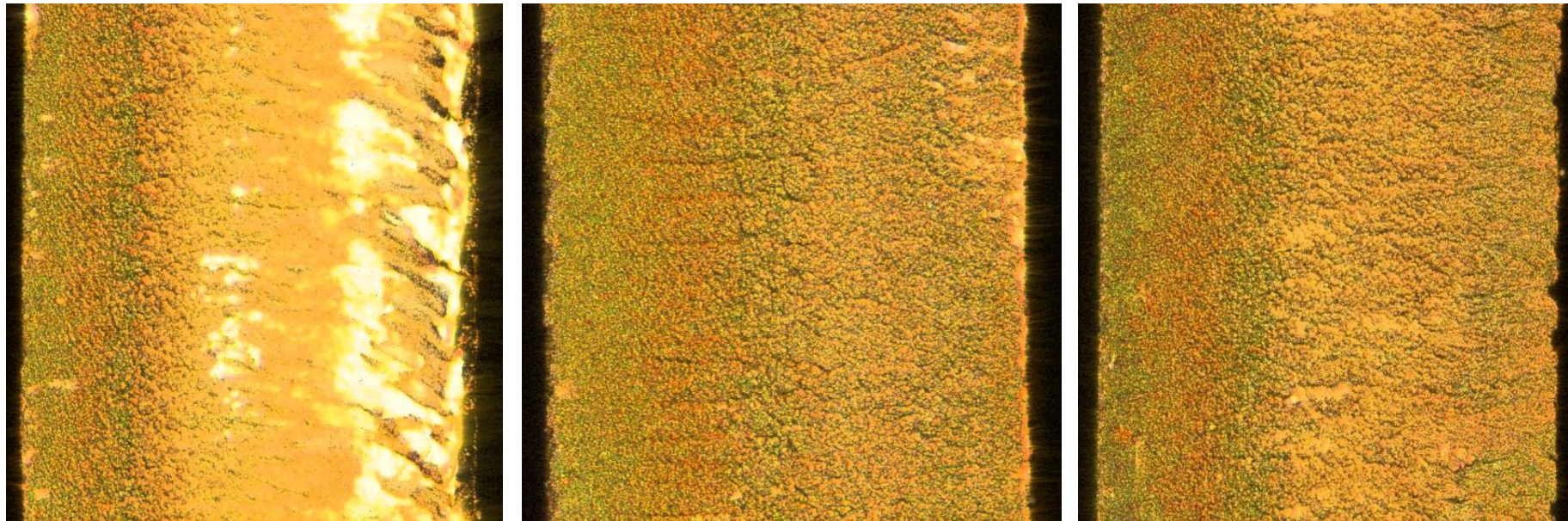
Investigate ablation mechanism

Influence of processing parameters

Generate input for upscaling

Task 2.2: Process limits fine cutting of metals

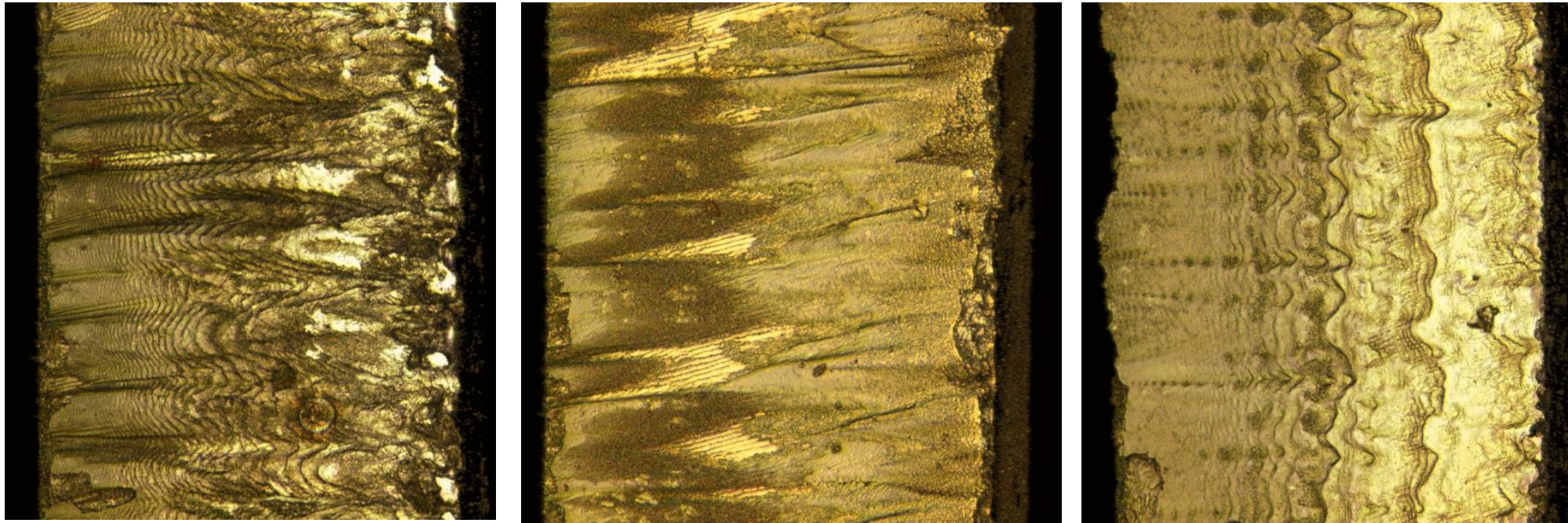
- Improvement in surface quality with increasing pulse energy: Brass



Images of the cut surfaces for varying pulse energy. (From L-R) 35 μ J, 65 μ J, 83 μ J. Keyence VK-8710K Laser scanning microscope, 20x objective.

Task 2.2: Process limits fine cutting of metals

- Improvement in surface quality with increasing pulse energy: Steel



Images of the cut surfaces for varying pulse energy. (From L-R) 35 μJ , 65 μJ , 83 μJ . Keyence VK-8710K Laser scanning microscope, 20x objective.

Task 2.2: Process limits fine cutting of metals

- Objectives:

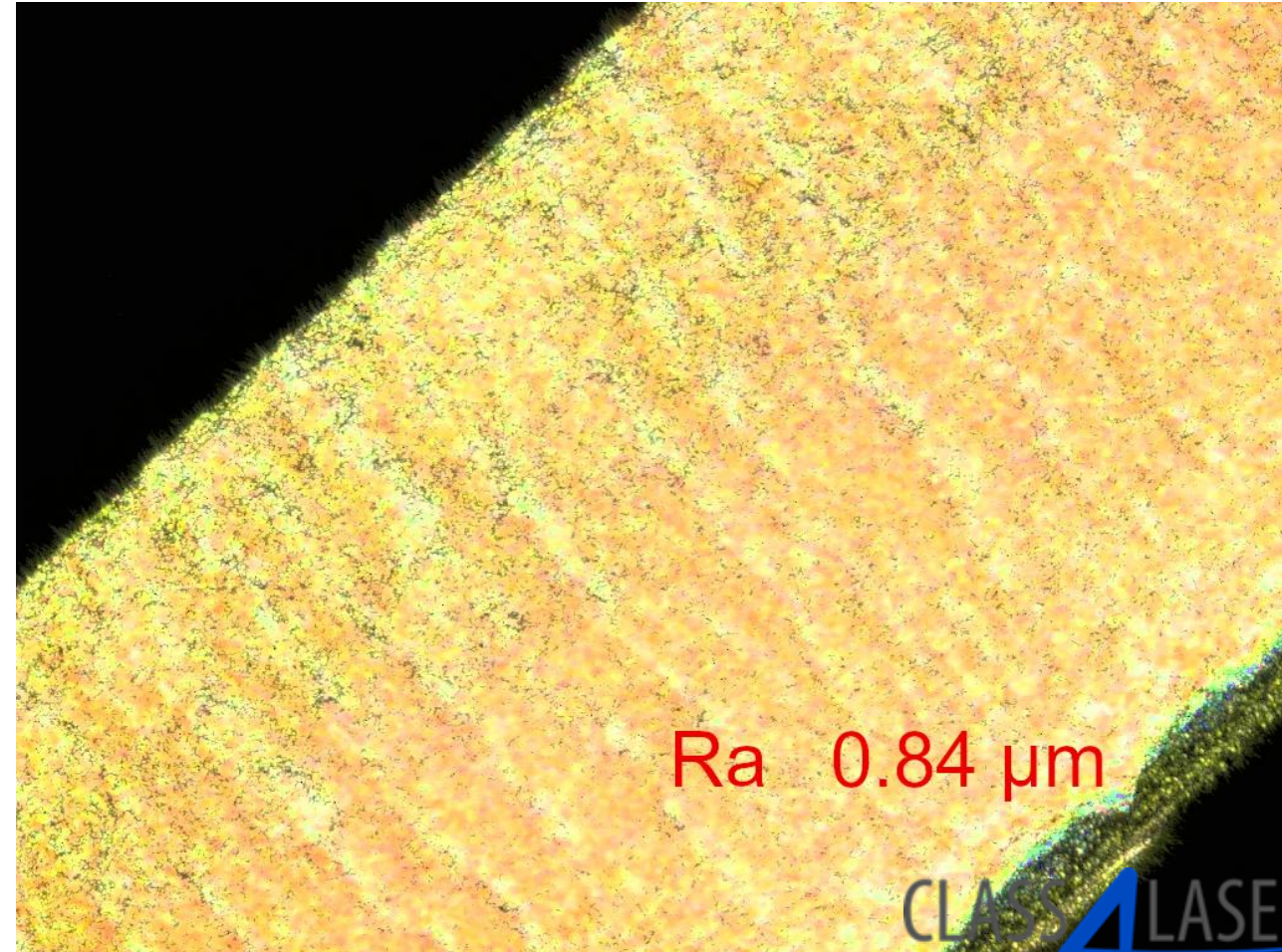
Fundamental process development

Investigate ablation mechanism

Influence of processing parameters

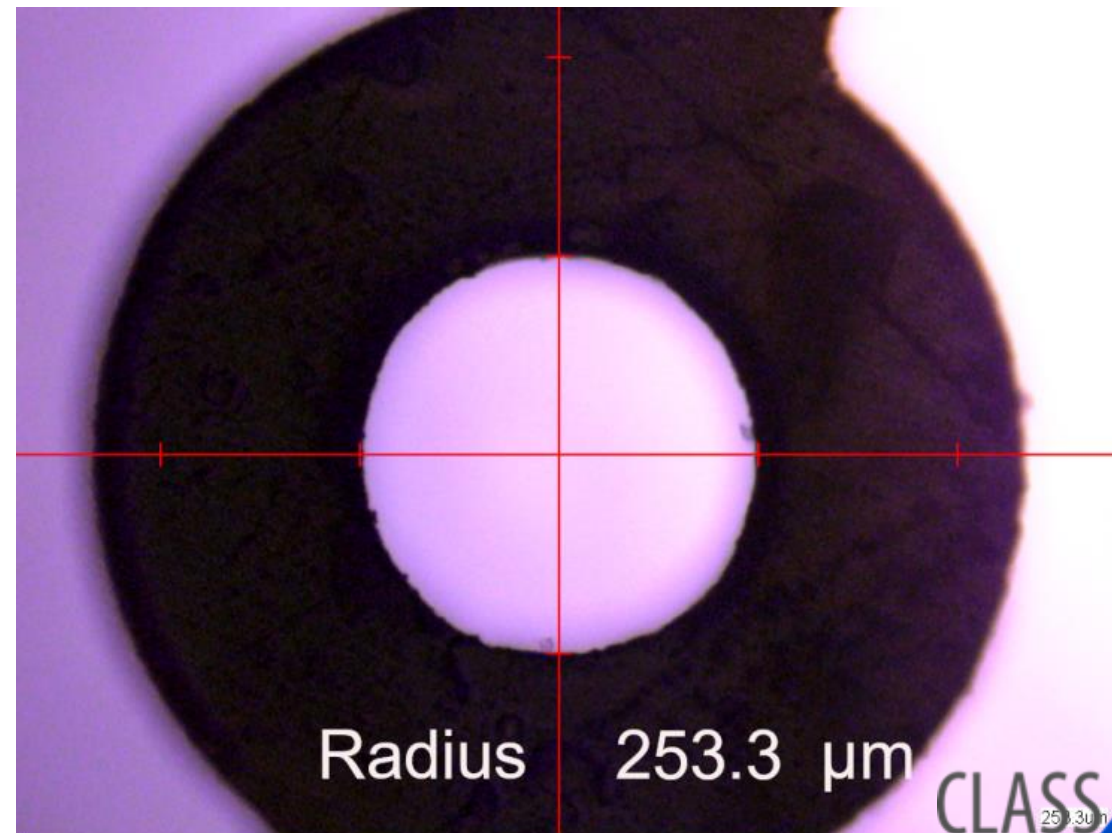
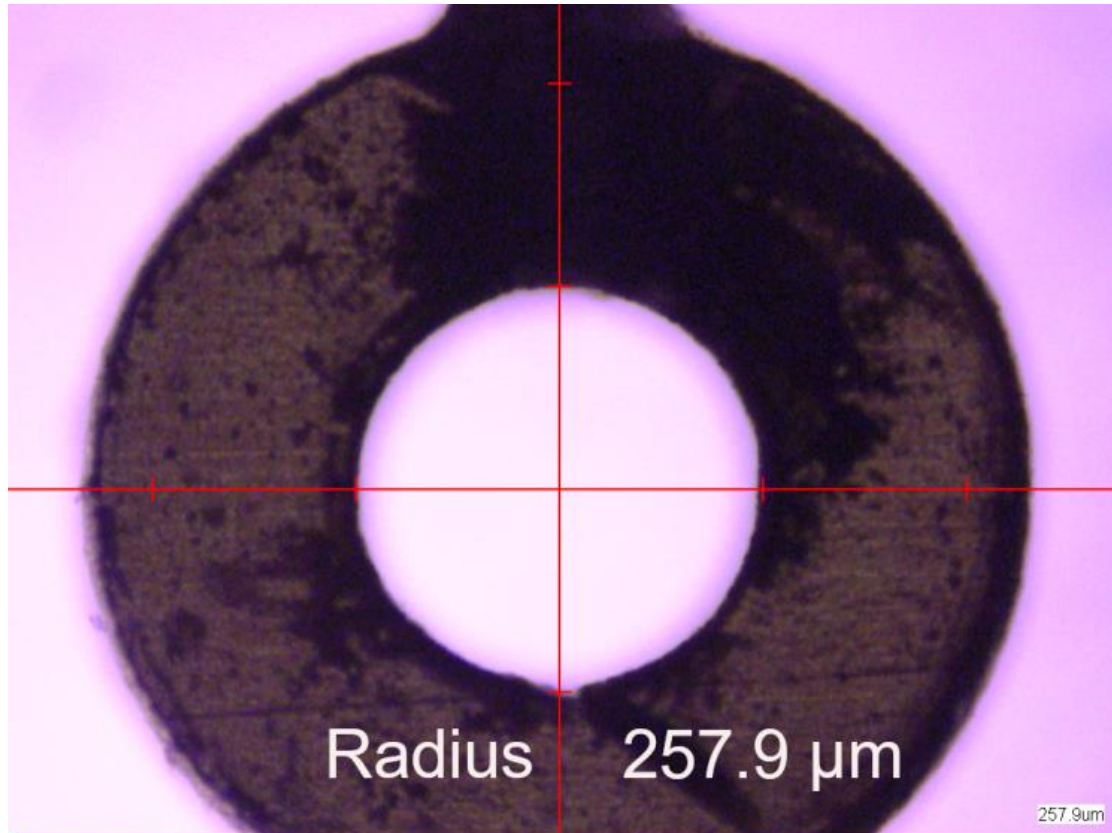
Generate input for upscaling

MS26 High quality fine cutting of metal with low average power

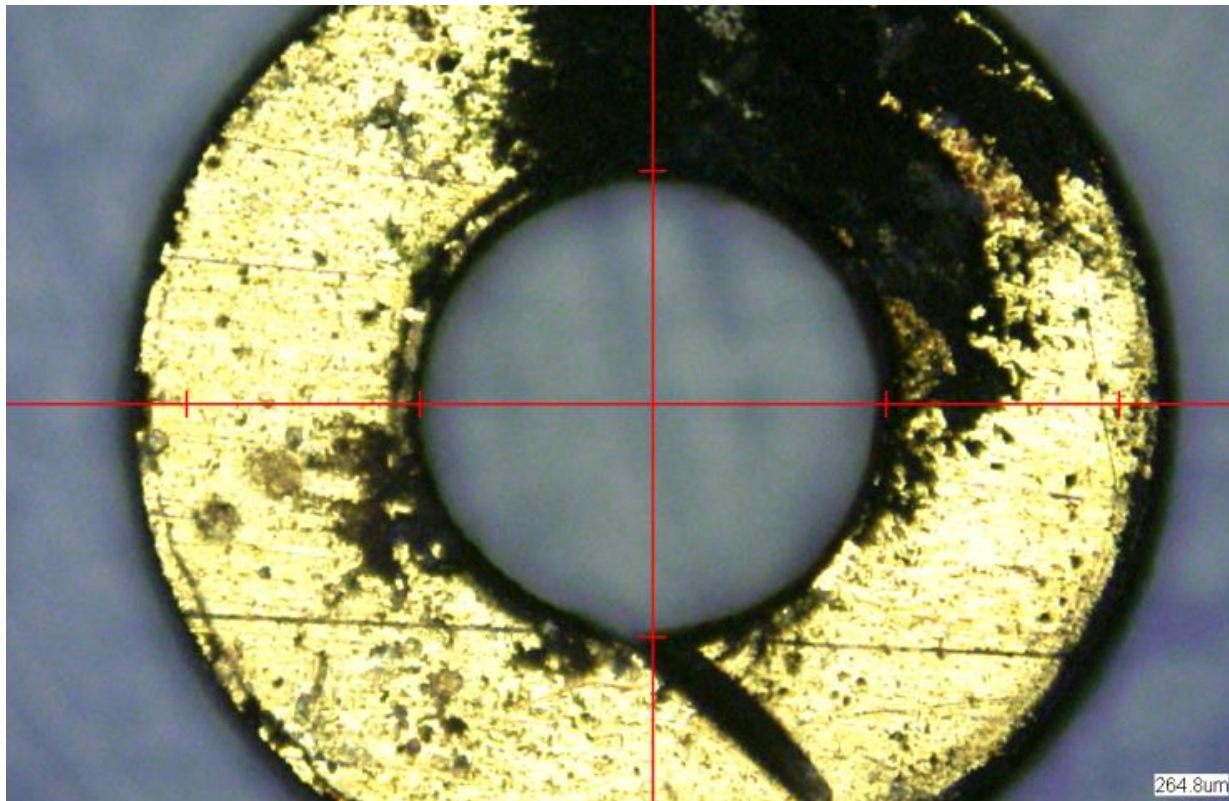


Images of the cut surface. Keyence VK-8710K Laser scanning microscope, 50x objective

MS26 High quality fine cutting of metal with low average power



MS26 High quality fine cutting of metal with low average power



MS26 High quality fine cutting of metal with low average power

No.	KPI	Values	Status
2	Surface roughness (functional/non-functional)	Expected : $R_a \leq 0.1 \mu\text{m} / 0.4 \mu\text{m}$	✓
		Validated : $R_a < 1 \mu\text{m} / 1 \mu\text{m}$	
		Not validated : $R_a \geq 1 \mu\text{m}$	
3	Shape deviation	Expected : $< \pm 2 \mu\text{m}$	✓
		Validated : $< \pm 5 \mu\text{m}$	
		Not validated : $> \pm 5 \mu\text{m}$	
4	Taper	Expected : 0°	✓
		Validated : Within dimension tolerances	
		Not validated : Above dimension tolerances	
5	Colouration	Expected : None	✓
		Validated : Washable surface oxidation	
		Not validated : Persistent surface oxidation	
6	Untying of part	Expected : Fall down in US-bath	✓
		Validated : Fall down in US-bath with separation cut	
		Not validated : Mechanical removal	

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Partners involved:



BOSCH



Task 2.3: Fundamental process development diamond ablation

- Status

- | | | |
|-----------------------------|--------------------|---|
| • T2.3 | Complete |  |
| • D2.3 confidential version | Document submitted |  |
| • D2.3 public version | Document submitted |  |

Work presented at the PhotonicWest 2018

William Scalbert, David Tanner, Fathima Laffir, Ronald Holtz, "Development of high power laser ablation process for polycrystalline diamond polishing: Part 1. Fundamental understanding of PCD ultra-short pulsed laser ablation," Proc. SPIE 10525, High-Power Laser Materials Processing: Applications, Diagnostics, and Systems VII, 105250N (15 February 2018); doi:10.1117/12.2290197

Task 2.3: Fundamental process development diamond ablation

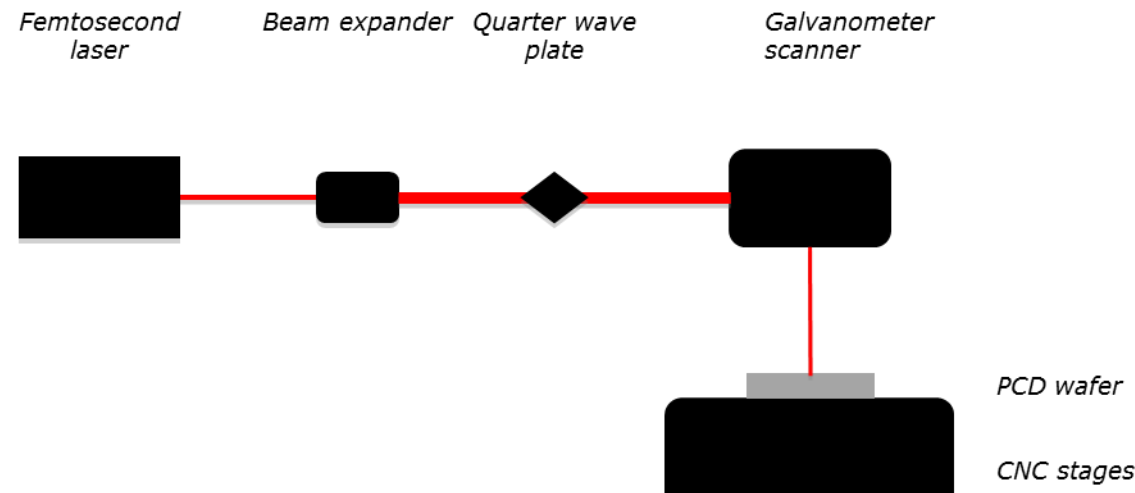
- Experimental set up
 - Three Element Six PCD grades tested

PCD Grade Name	Average Grain Size (µm)	Diamond Content (wt %)	Cobalt Content (wt%)
CMX850	1	80	20
CTB010	12	90	10
CTM025	30	90	10

- Grades presenting highest variation in diamond grain size and diamond content

Task 2.3: Fundamental process development diamond ablation

- Experimental set up
 - Ablation trials with low power ultra-short pulsed laser

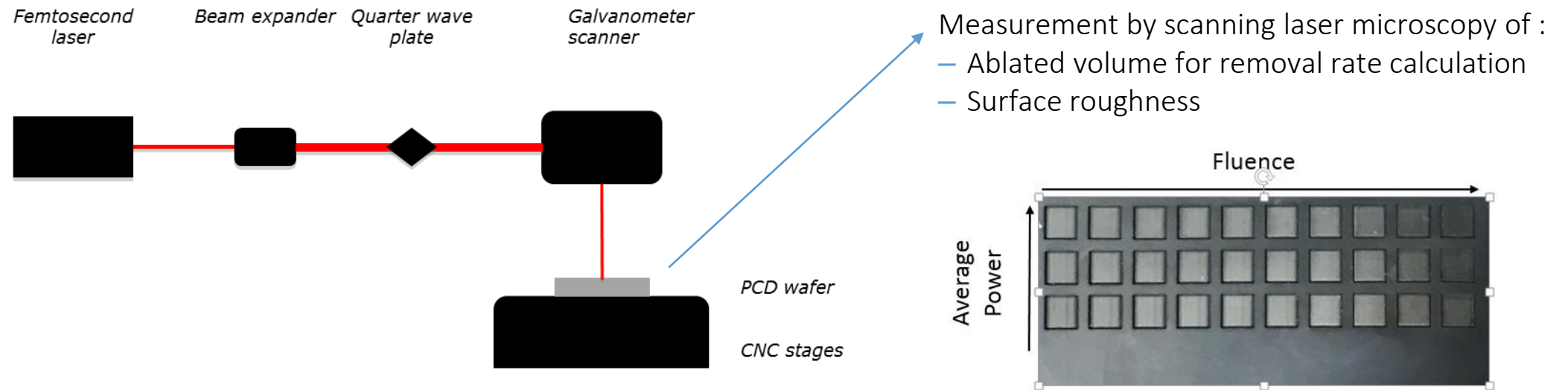


Characteristics of the femtosecond laser used in T2.3:

Wavelength	1030nm
Pulse length	230fs – 10ps
Maximum average power	5W
Frequency	60kHz – 1MHz
Polarization	Circular
M ²	< 1.2

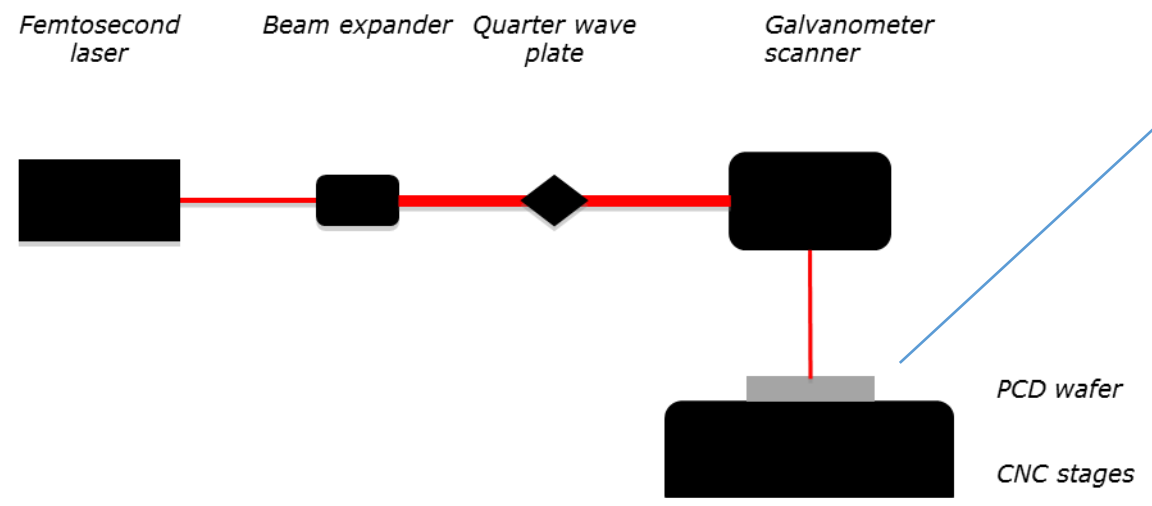
Task 2.3: Fundamental process development diamond ablation

- Experimental set up
 - Ablation trials with low power ultra-short pulsed laser

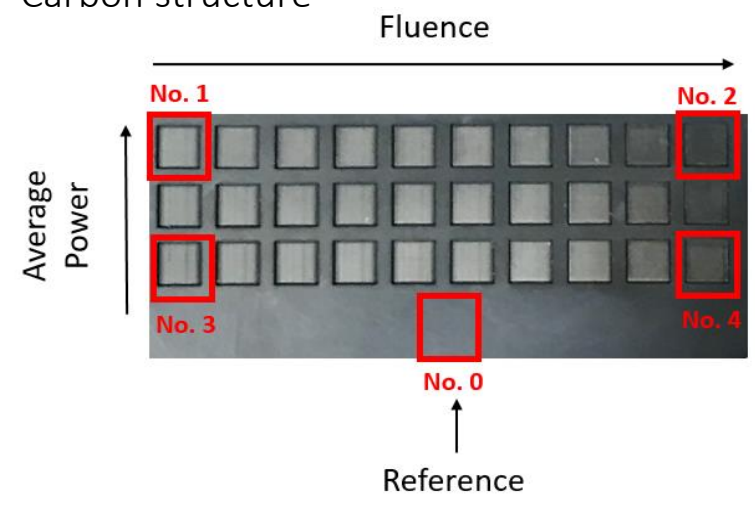


Task 2.3: Fundamental process development diamond ablation

- Experimental set up
 - Ablation trials with low power ultra-short pulsed laser

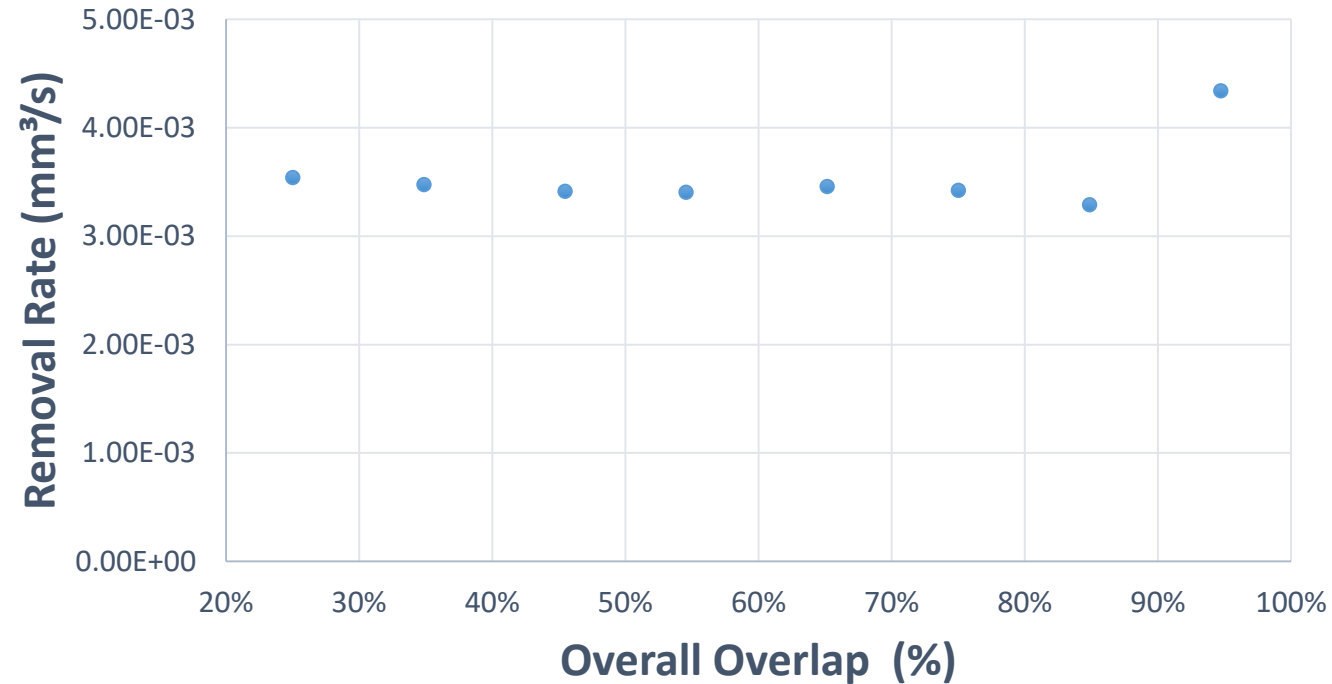


Physicochemical characterisation by Raman spectroscopy :
 — Carbon structure



Task 2.3: Fundamental process development diamond ablation

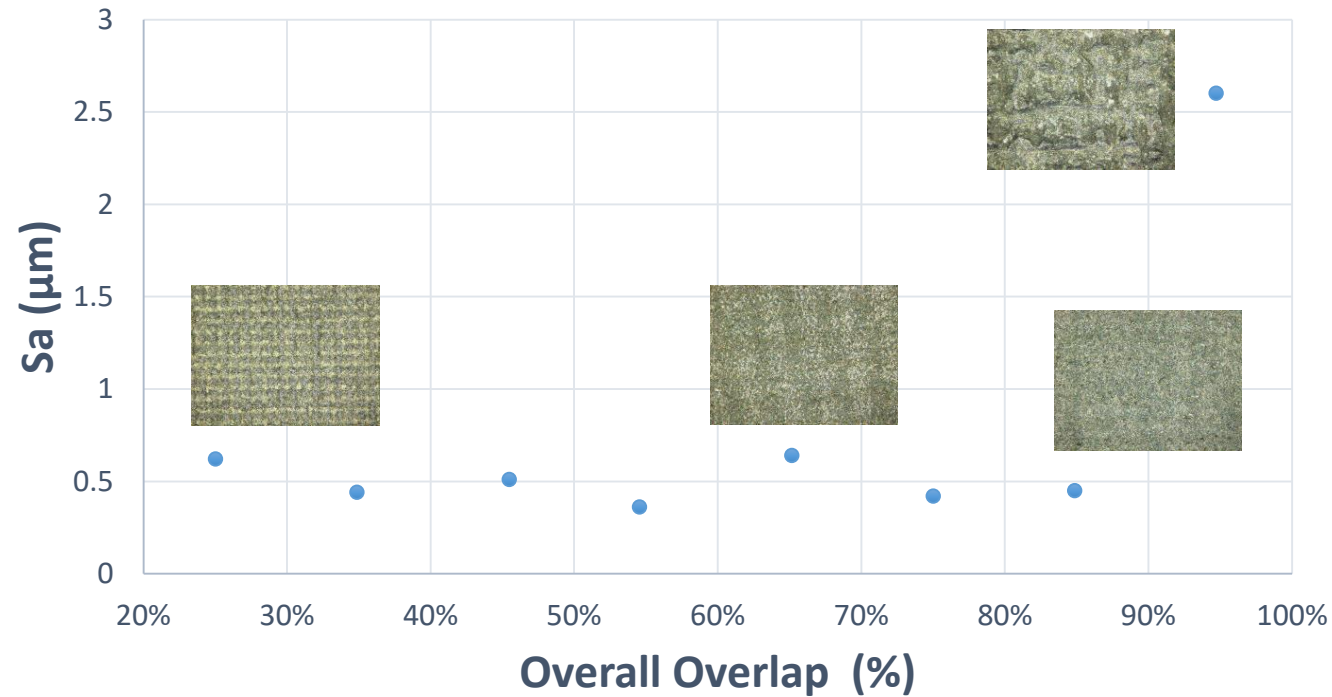
- Influence of Heat Accumulation
 - Increase of ablation rate with heat accumulation



Over 95% overlap :
— Increase of ablation rate

Task 2.3: Fundamental process development diamond ablation

- Influence of Heat Accumulation
 - Increase of ablation rate with heat accumulation



Over 95% overlap :
 — Increase of ablation rate
 — Surface critically damaged

HEAT ACCUMULATION EFFECT

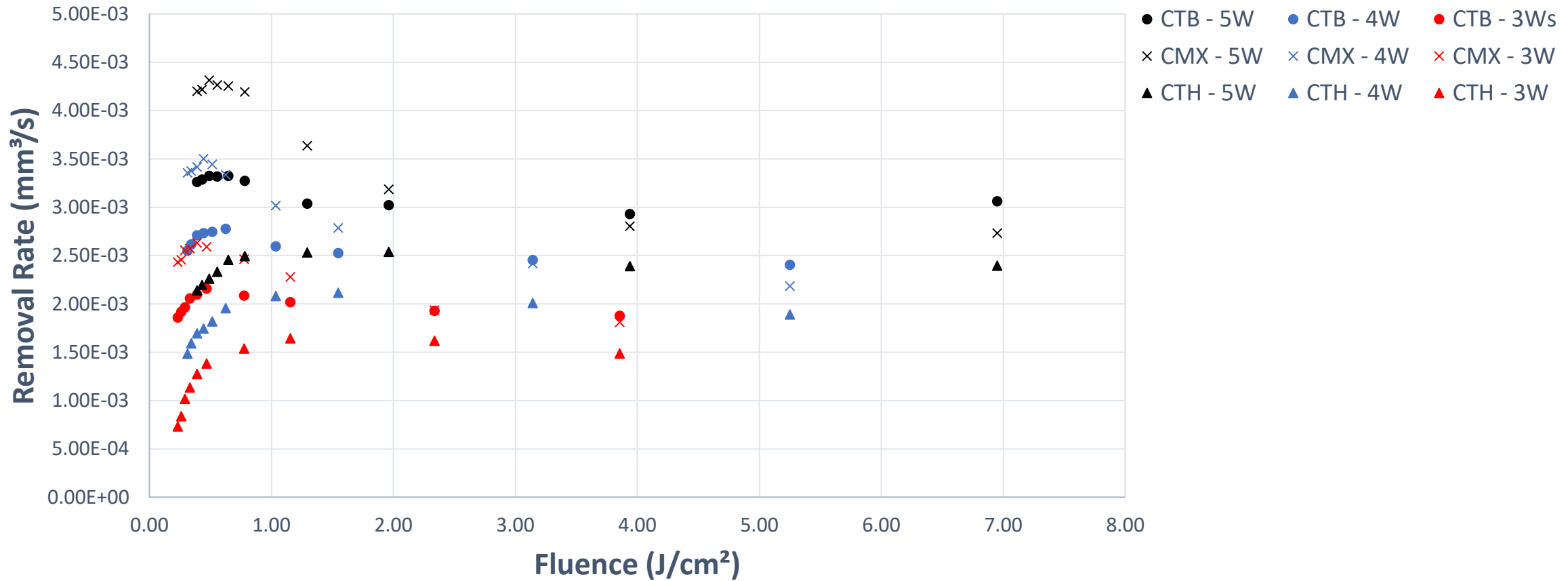
Task 2.3: Fundamental process development diamond ablation

- Variation of Ablation Rate with PCD grades
 - PCD grades

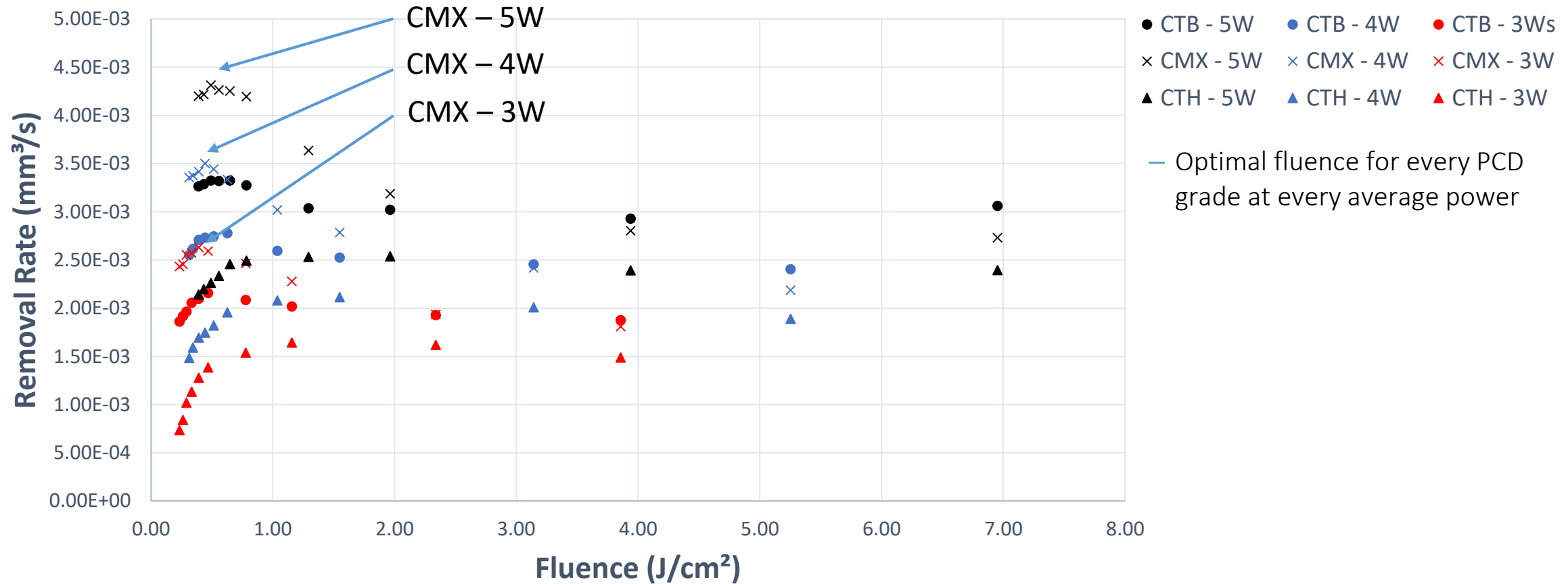
PCD Grade Name	Average Grain Size (µm)	Diamond Content (wt %)	Cobalt Content (wt%)
CMX850	1	80	20
CTB010	12	90	10
CTM025	30	90	10

- Measurements of the ablation rate variation with fluence

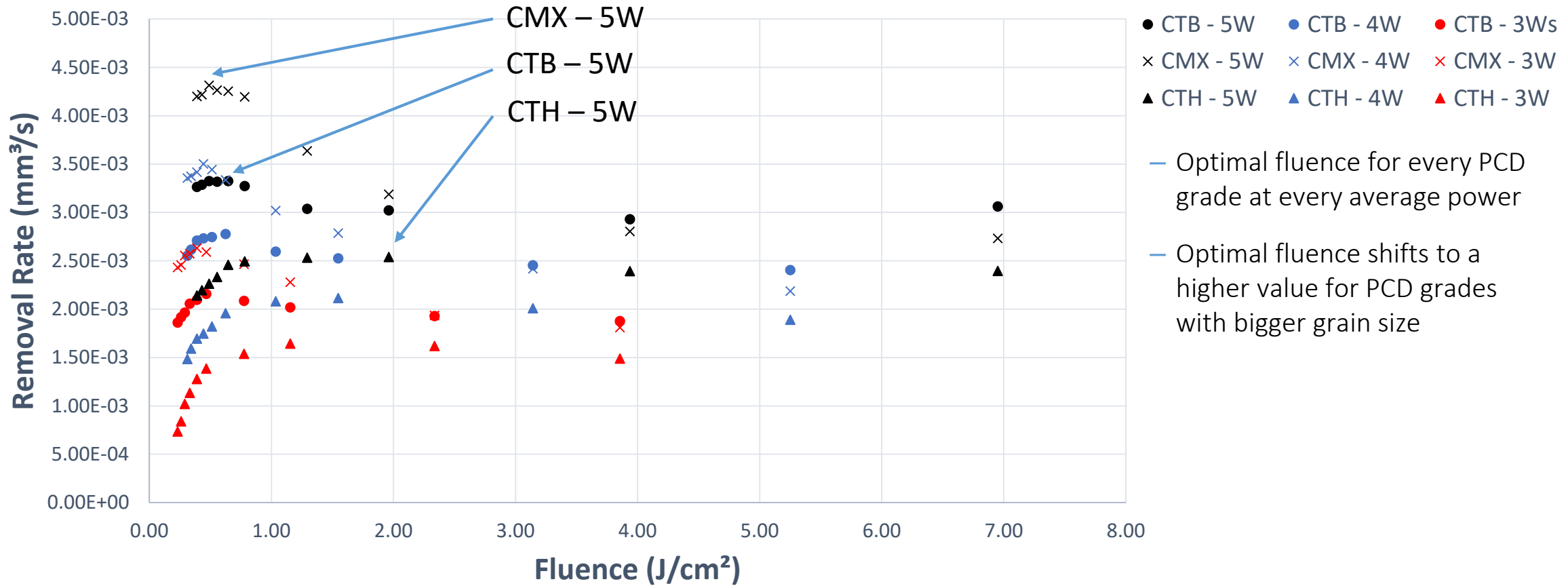
Task 2.3: Fundamental process development diamond ablation



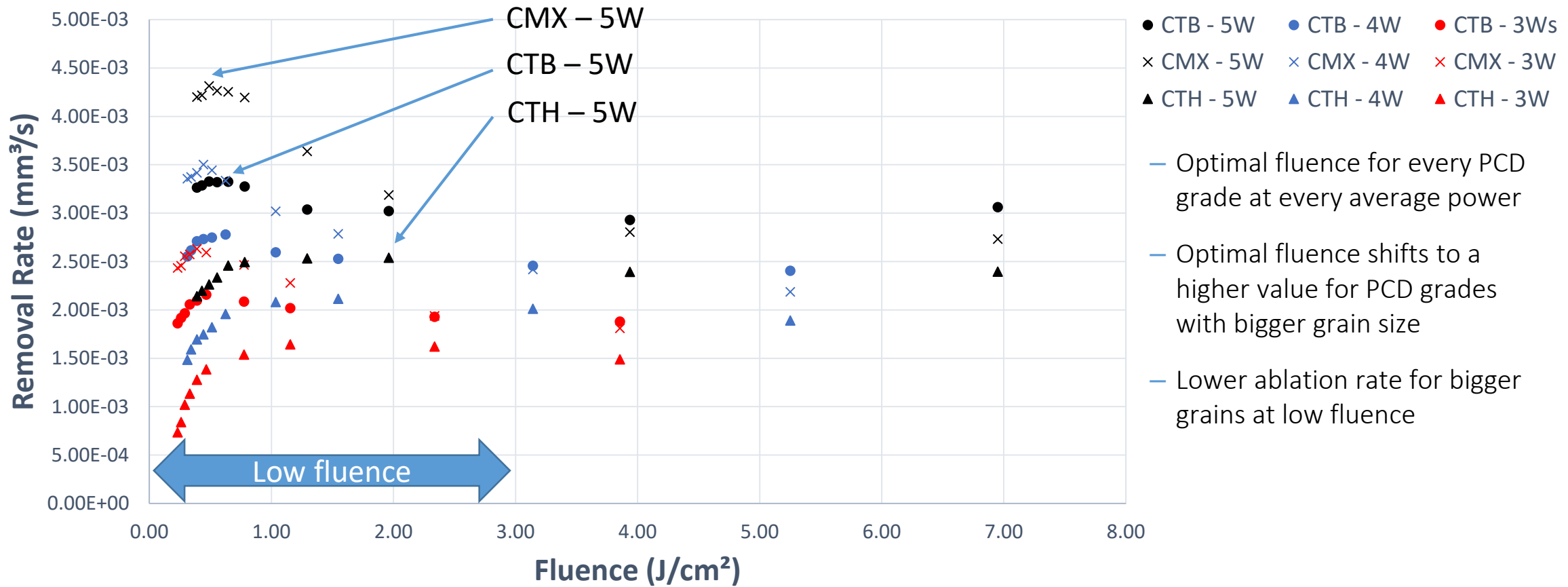
Task 2.3: Fundamental process development diamond ablation



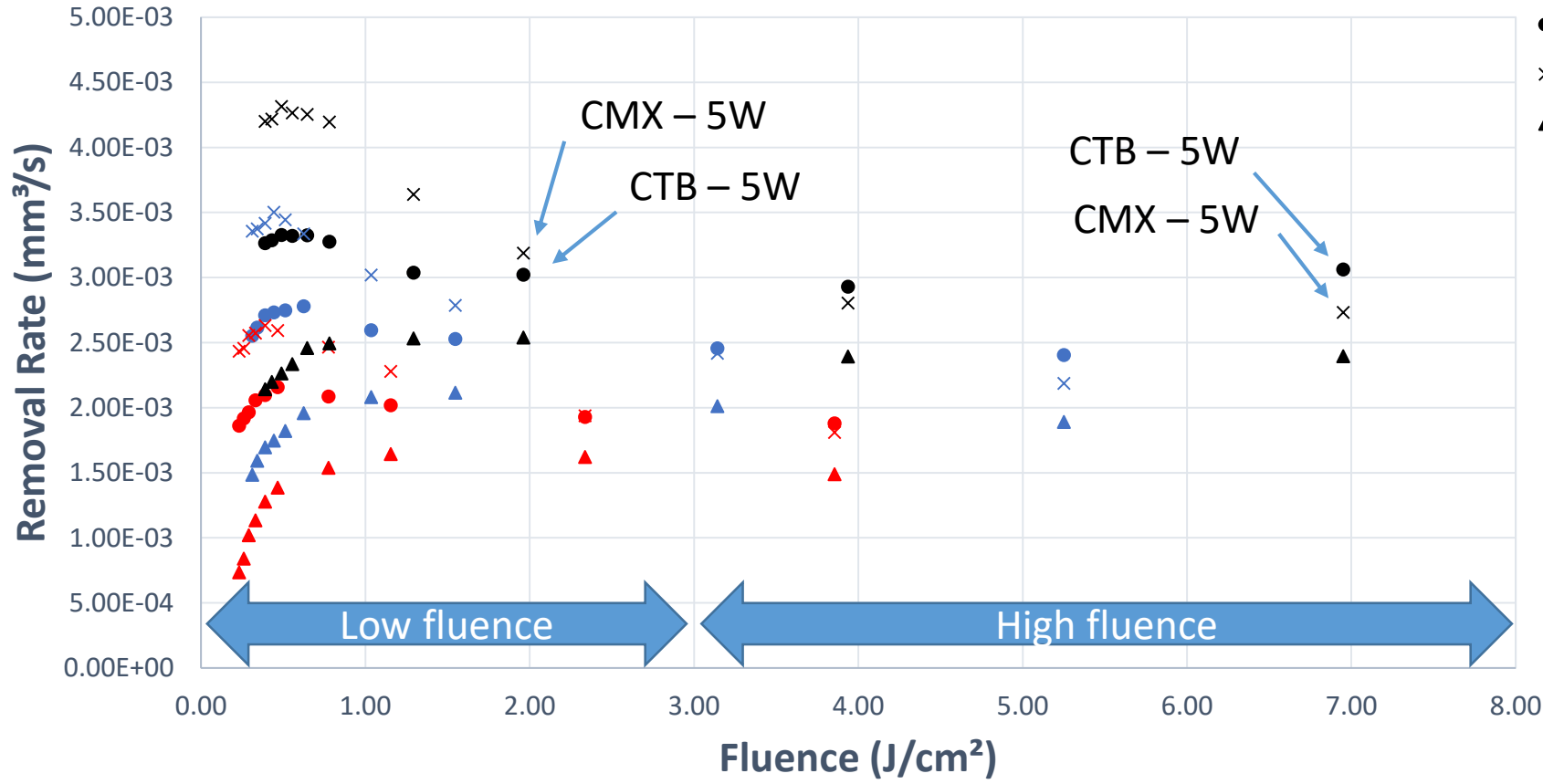
Task 2.3: Fundamental process development diamond ablation



Task 2.3: Fundamental process development diamond ablation



Task 2.3: Fundamental process development diamond ablation



- Optimal fluence for every PCD grade at every average power
- Optimal fluence shifts to a higher value for PCD grades with bigger grain size
- Lower ablation rate for bigger grains at low fluence
- Higher ablation rate for grades with higher diamond content at high fluence

Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
 - Two steps processing
 - Polishing to be achieved with spot size below 10 μm
 - Optimal fluence expected between 0.5 J/cm^2 and 1 J/cm^2 for processing at high power
 - High power laser over 100 μJ pulse energy
 - Fluence over 1 J/cm^2 with 100 μJ and spot of 10 μm
 - So two processing steps required:
 1. Smoothing step will be performed with large spot size at high pulse energy/high average power
 2. Finishing step will be performed with small spot at low pulse energy/low average power

Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
 - Maximum spot size

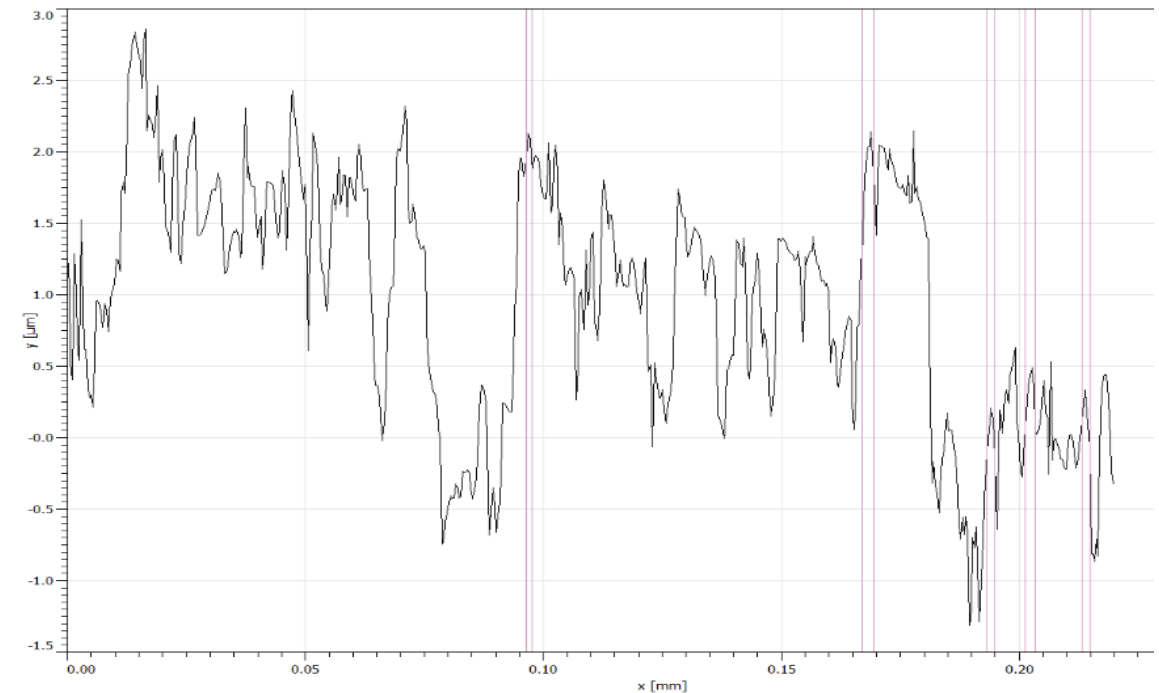
$$d = 2 \sqrt{\frac{E}{\pi F}}$$

Average power: $P = 200\text{W}$
 Frequency: $f = 2\text{MHz}$
 Pulse energy: $E = 100\mu\text{J}$

Optimal fluence: $F =$	0.49J/cm⁻²	1J/cm⁻²	2J/cm⁻²
Spot diameter: $d =$	160μm Maximal spot size	112μm	80μm

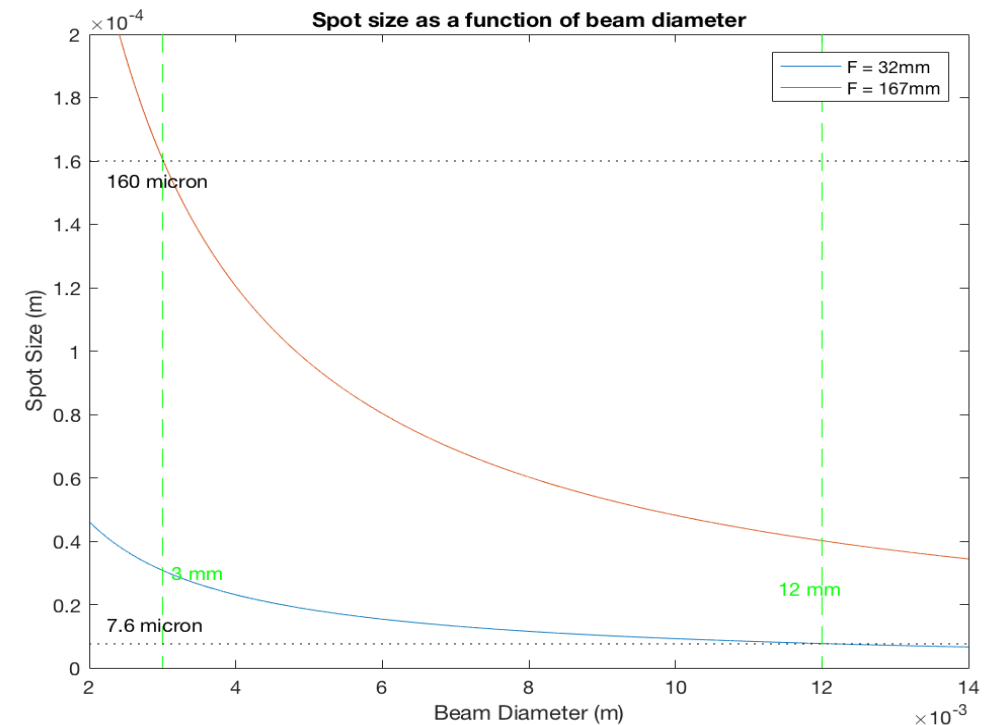
Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
 - Minimum spot size
 - Topography of lapped PCD wafer
 - Peak with an average width of $1\mu\text{m}$
 - Optimal minimum spot size $1\mu\text{m}$
 - Not corresponding to final ablated surface prior to laser-polishing



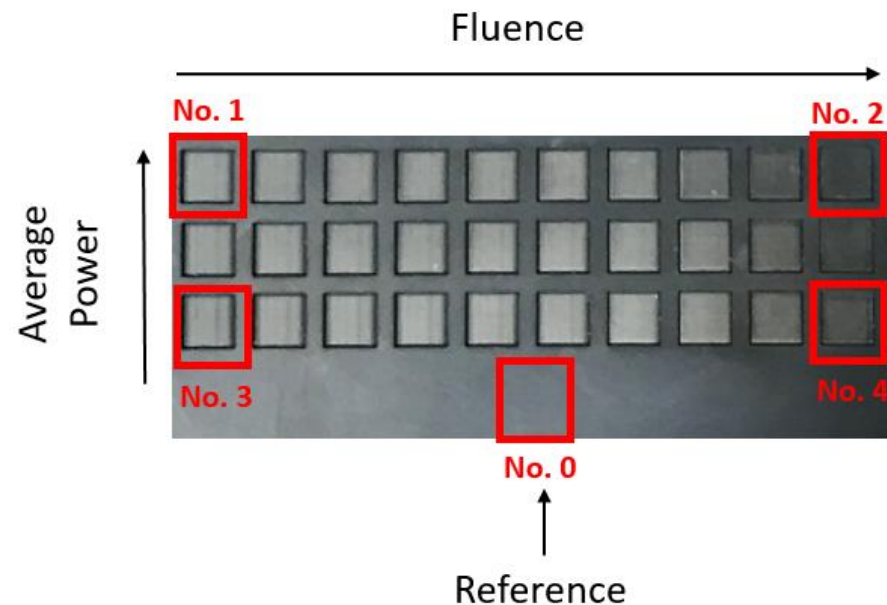
Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
 - Limitation in spot size and speed
 - Minimum can only reach 7.6 μm .
Not critical as topography after ablation at high power is yet unknown.
The goal was to determine smallest spot achievable on this system.
 - Maximum reaches 160 μm .
Match the requirement of spot diameter to work close to the optimal fluence at high pulse energy



Task 2.3: Fundamental process development diamond ablation

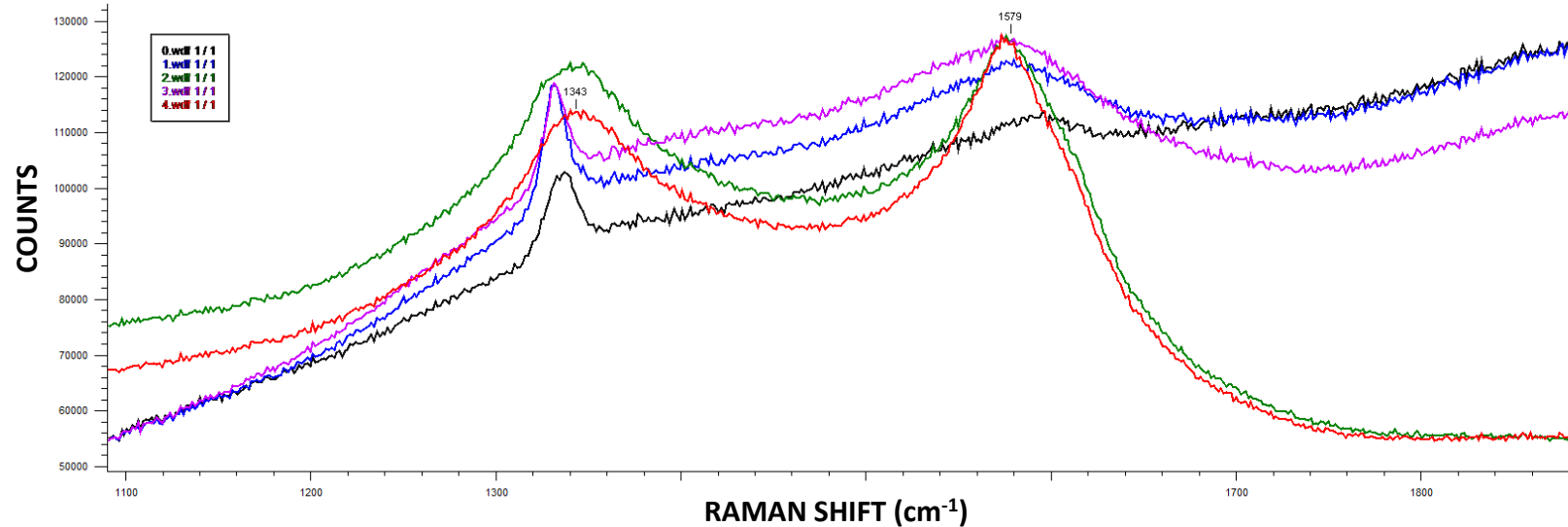
- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - Raman spectroscopy analyses



Area 0	Reference point (initial surface)	Lapped surface for CMX850* EDM ground surface for CTB010*
Sample 1	High power – Low fluence	5W – 0.39 J/cm ⁻²
Sample 2	High power – High fluence	5W – 6.95J/cm ⁻²
Sample 3	Low power – Low fluence	3W – 0.23J/cm ⁻²
Sample 4	Low power – High fluence	3W – 3.86J/cm ⁻²

Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - SEM/Raman Spectrometer Measurements



CMX850

1 μ m grain size,

80% wt diamond content

Area 0 Initial surface

Sample 1 5W – low fluence

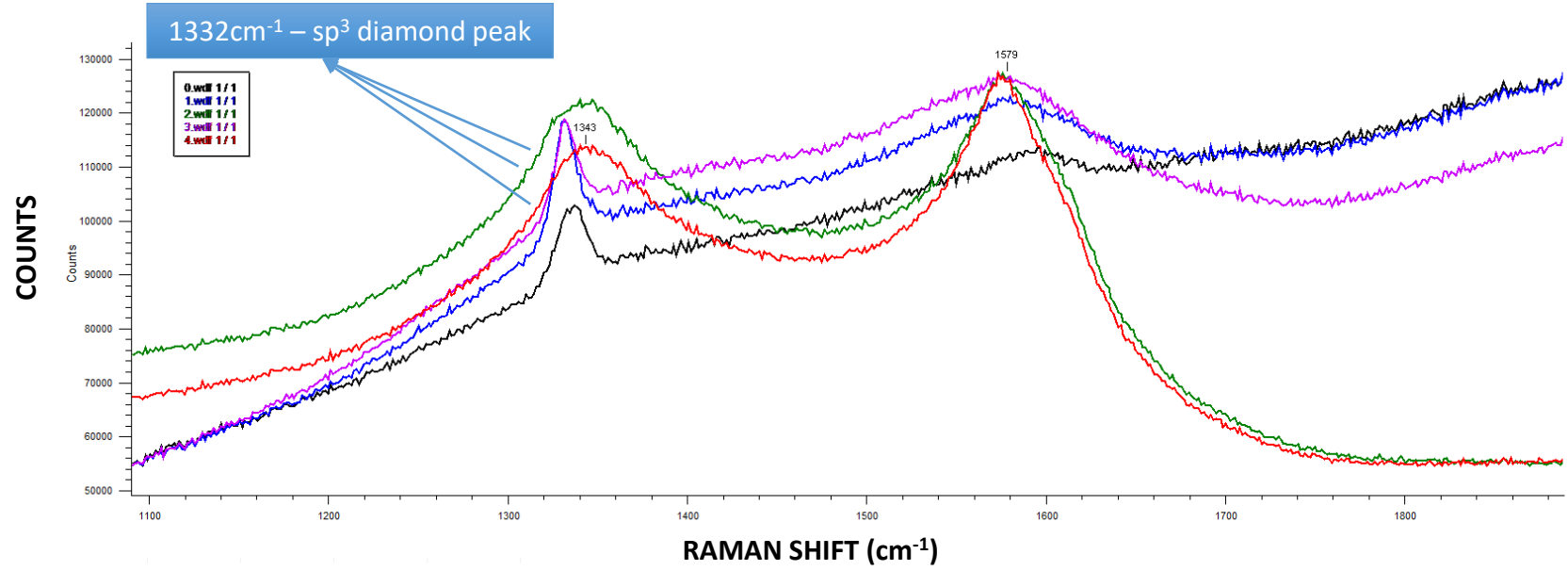
Sample 2 5W – high fluence

Sample 3 3W – low fluence

Sample 4 3W – high fluence

Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - SEM/Raman Spectrometer Measurements

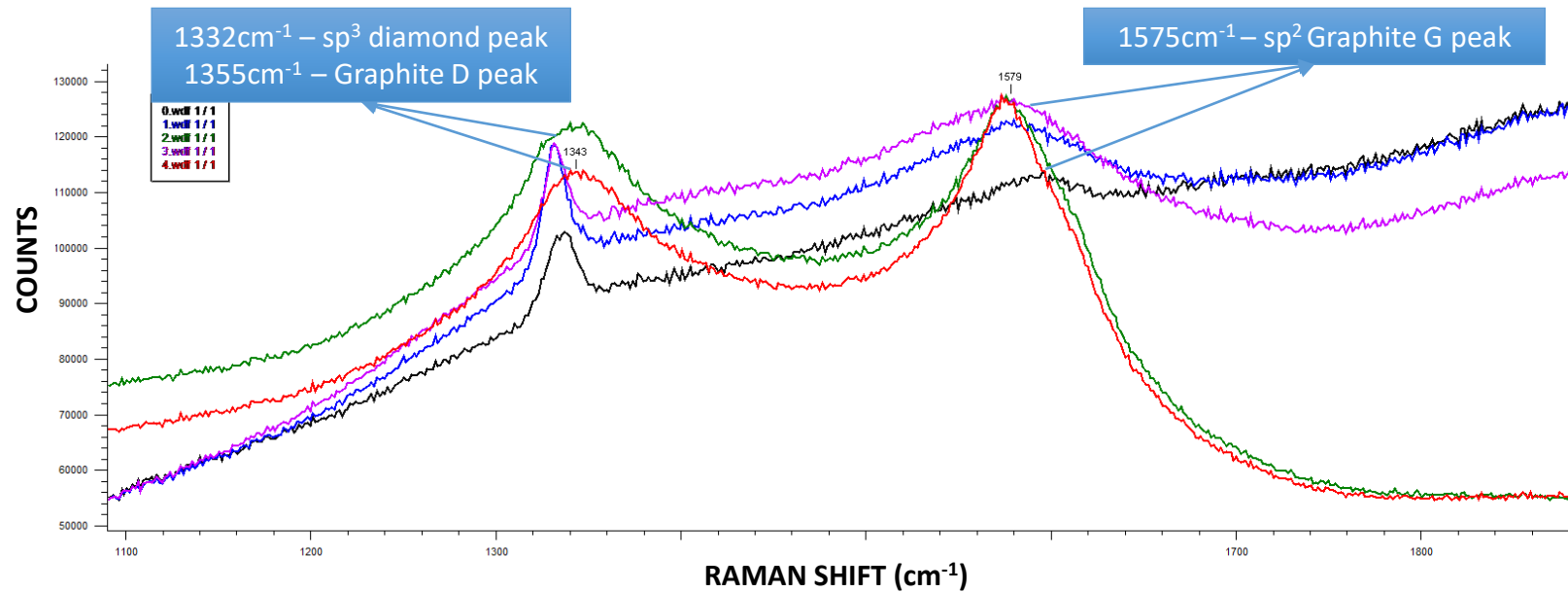


CMX850
 1µm grain size,
 80% wt diamond content

- Area 0 Initial surface
- Sample 1 5W – low fluence
- Sample 2 5W – high fluence
- Sample 3 3W – low fluence
- Sample 4 3W – high fluence

Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - SEM/Raman Spectrometer Measurements



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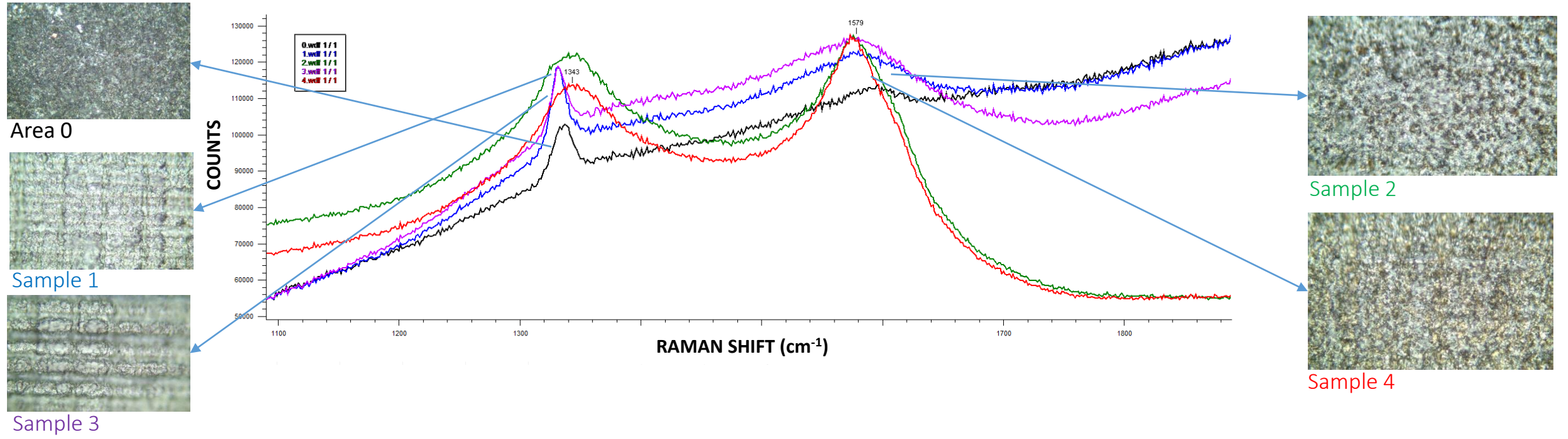
Sample 2 5W – high fluence

Sample 3 3W – low fluence

Sample 4 3W – high fluence

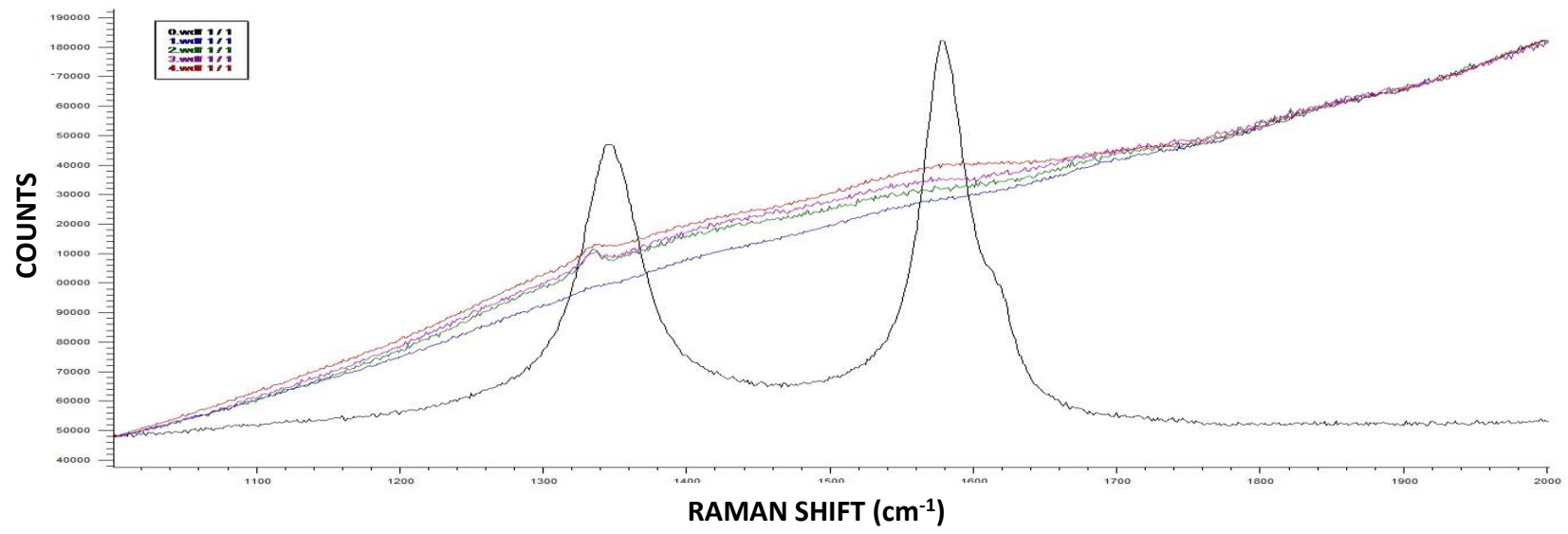
Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - SEM/Raman Spectrometer Measurements



Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
 - SEM/Raman Spectrometer Measurements



CTB010
 12µm grain size,
 90% wt diamond content

- Area 0 Initial surface
- Sample 1 5W – low fluence
- Sample 2 5W – high fluence
- Sample 3 3W – low fluence
- Sample 4 3W – high fluence

Task 2.3: Fundamental process development diamond ablation

- Conclusion

Parameters	Current Performances	E6 Specifications	Specification agreed with partners
Wavelength	1030nm	1030nm	1030nm
Power	5W	200W	100W*
Pulse duration	230fs – 10ps	< 500 fs – 10ps	400fs – 10ps
Frequency	60kHz-1MHz	<2MHz	<2MHz
M ²	1.2	1.2	<1.3
Pulse burst	None	Pulse burst	Multi pulses burst
Maximum scanning speed	3000mm/s	<3000mm/s	3000mm/s
Spot diameter	20µm	2µm – 160µm	**7.6µm - 160µm
Polarization	Circular	Circular	Circular

*Agreement on delivery of industrial TANGOR laser with average power of 100W



Task 2.3: Fundamental process development diamond ablation

- Conclusion

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Polarization	Circular	Circular	Circular

**Due to optical limitations

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Partners involved:



BOSCH



Task 2.4: Upscaling of applications for high throughput - Si Processing

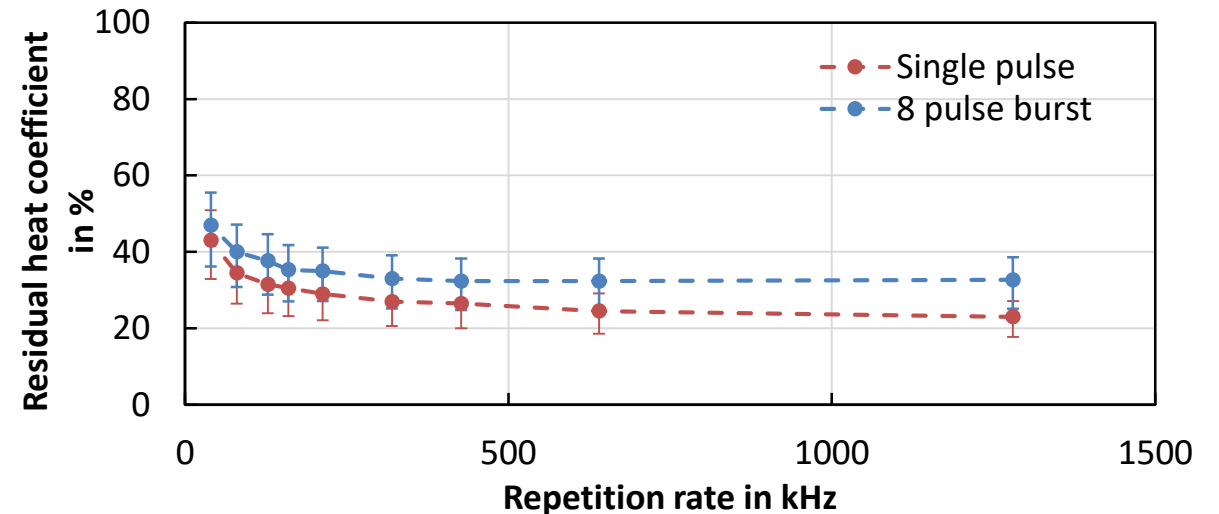
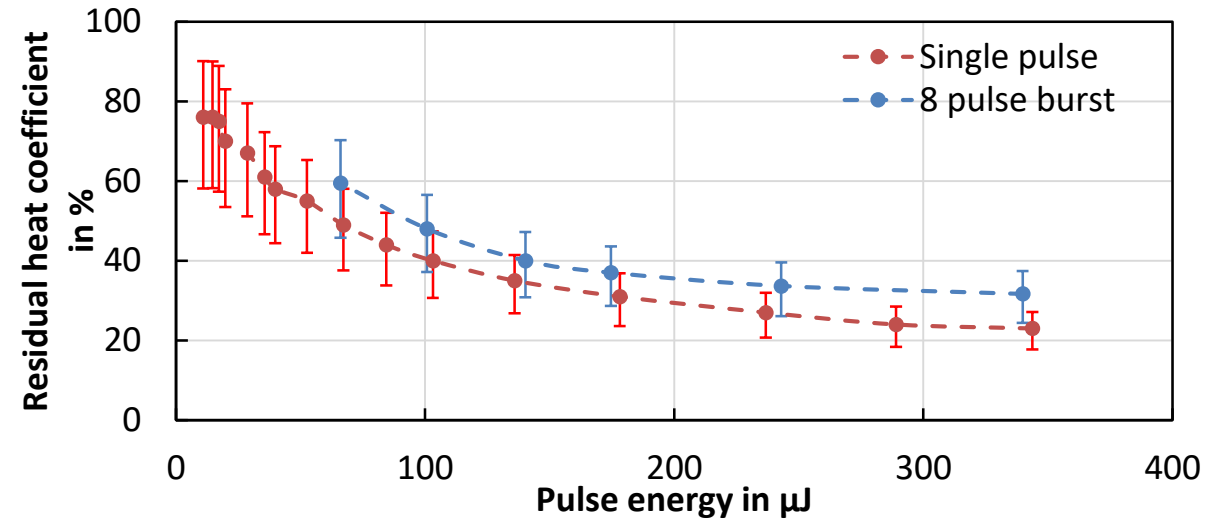
Heat accumulation – residual heat

- Calorimetric measurement of the residual heat
- Residual heat coefficient:

$$\eta_{resP} = \frac{E_{res}}{E_{P,total}}$$



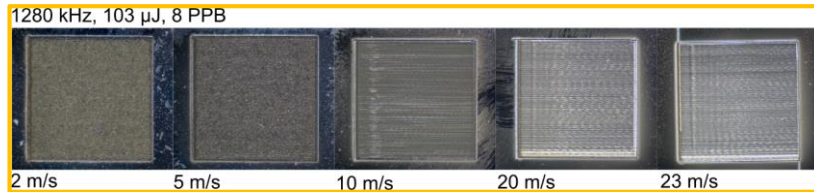
More heat generated using burst mode



Task 2.4: Upscaling of applications for high throughput

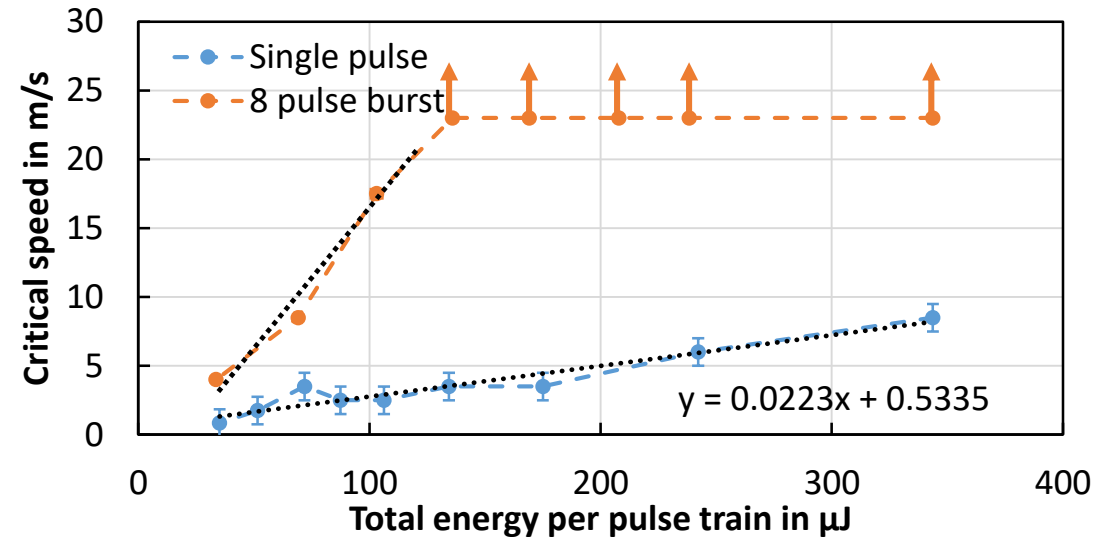
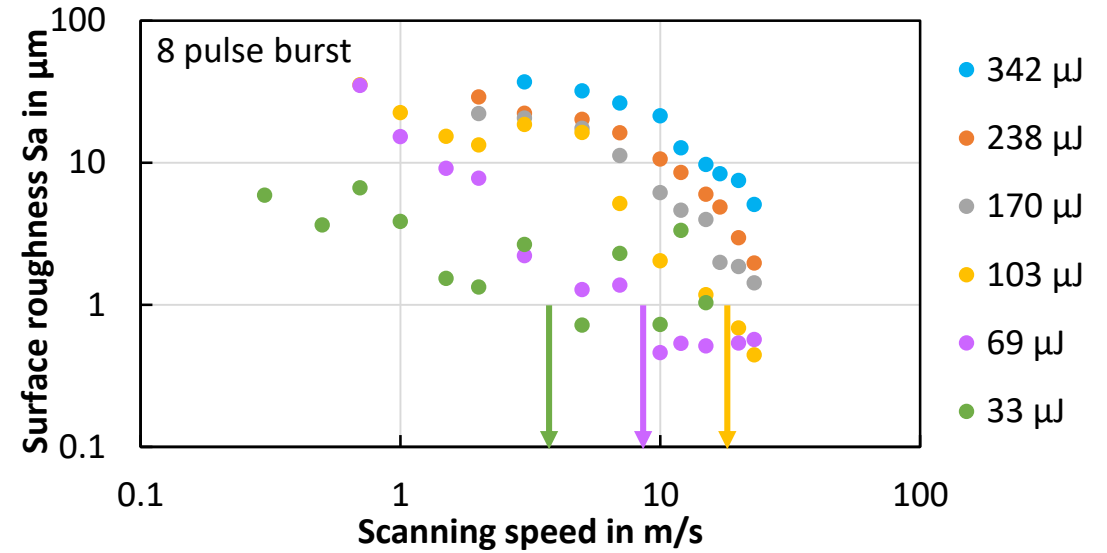
Heat accumulation between subsequent pulses – critical scanning speed

- Ablation of 5 mm x 5 mm squares with different speeds, pulse energies and repetition rates



- Evaluation of critical speed for HAP at Sa = 1 μm

➔ **Processing at 1 kW @ 1.28 MHz (1 PPB): 18 m/s**
Processing at 1 kW @ 1.28 MHz (8 PPB): 148 m/s



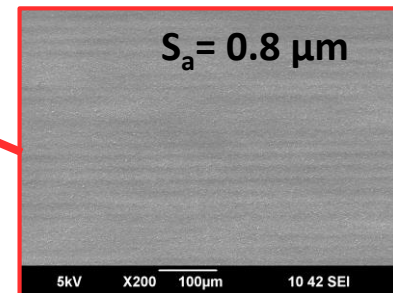
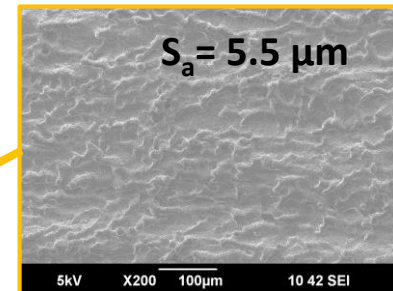
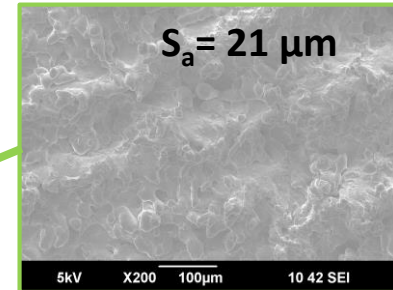
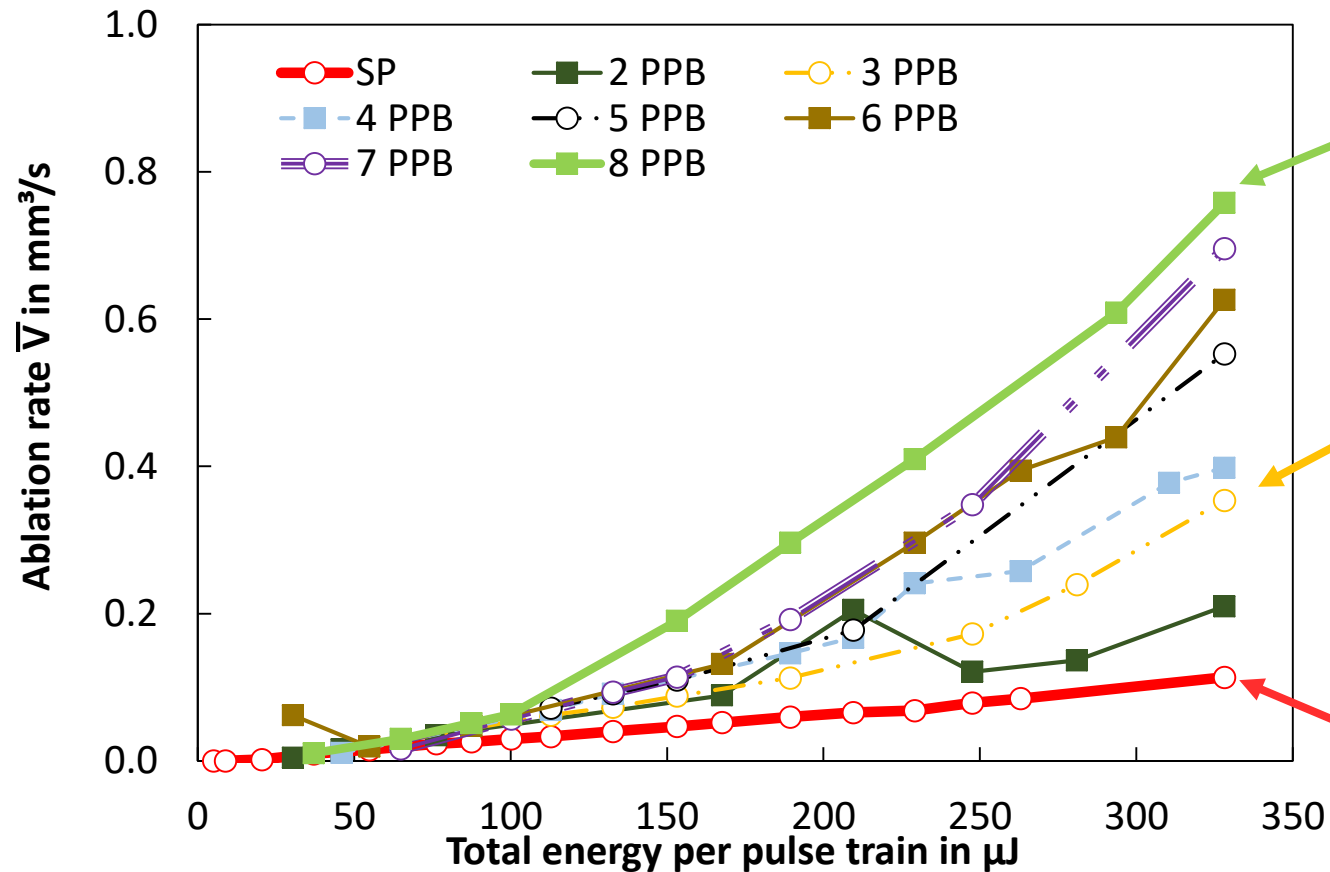
Task 2.4: Upscaling of applications for high throughput

Ablation rate

- Ablation of 5 mm x 5 mm squares with different numbers of pulses per burst, pulse energies and repetition rates

➔ More pulse energy leads to higher ablation rate

➔ Burst mode increases ablation rate significantly!



Task 2.4: Upscaling of applications for high throughput

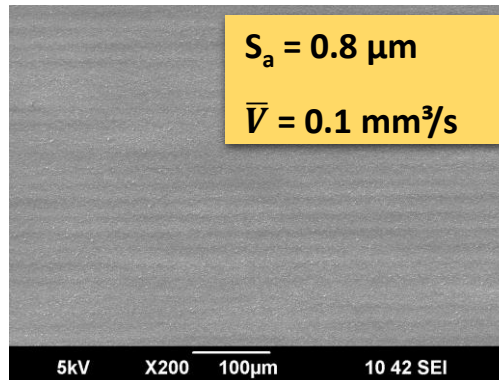
Upscaling strategies

1. Use scanning speeds near the critical speed for the HAP effect → **no HA**
2. Use burst mode with high number of pulses per burst → **high ablation rate**
3. Reduce fluence to an optimum value by increasing the focused beam diameter → **good surface quality**

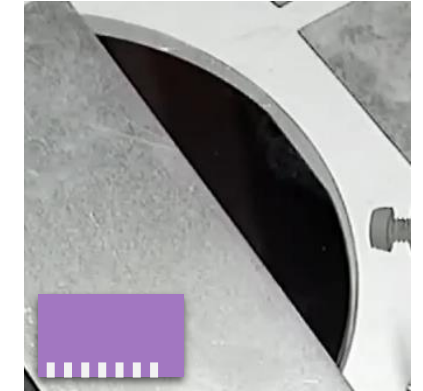
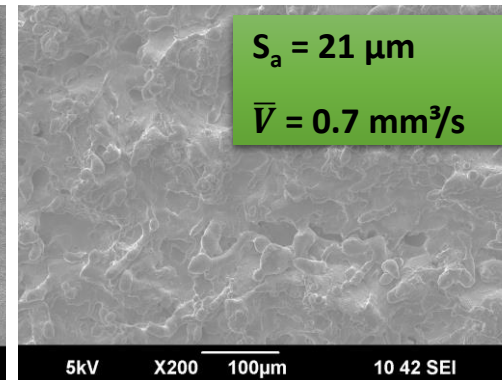
Outlook for further process improvement:
Two-step processing.



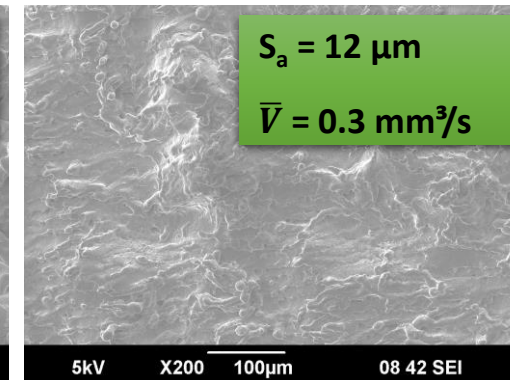
Single pulses
 $v_s = 9 \text{ m/s}$



7 pulses per burst
 $v_s = 9 \text{ m/s}$



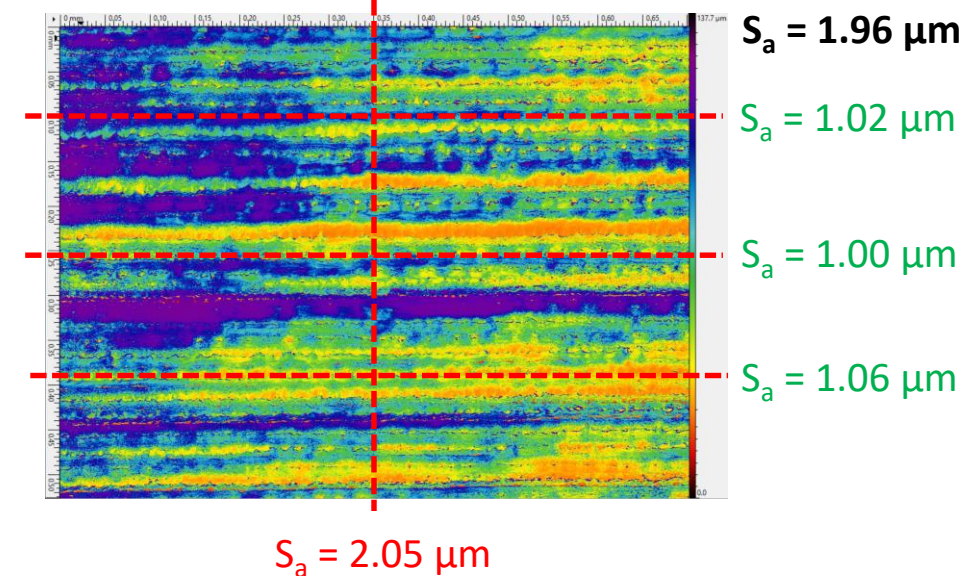
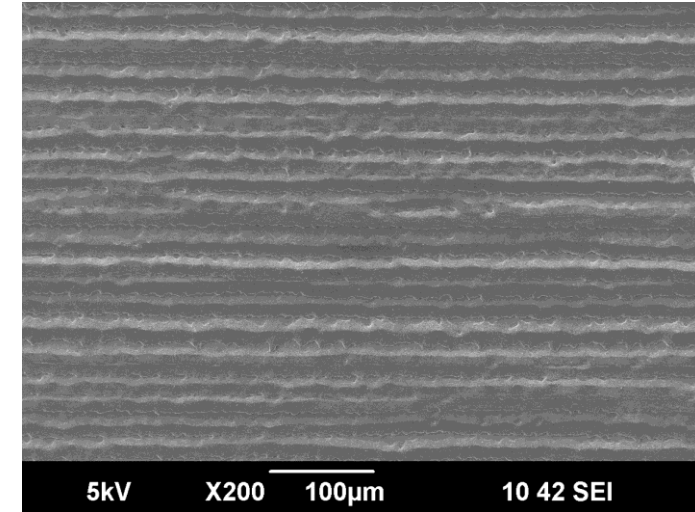
7 pulses per burst
 $v_s = 15 \text{ m/s}$



Task 2.4: Upscaling of applications for high throughput

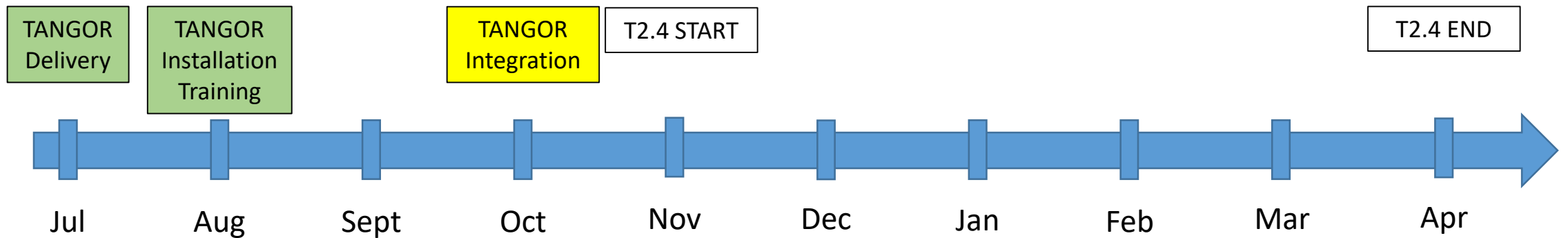
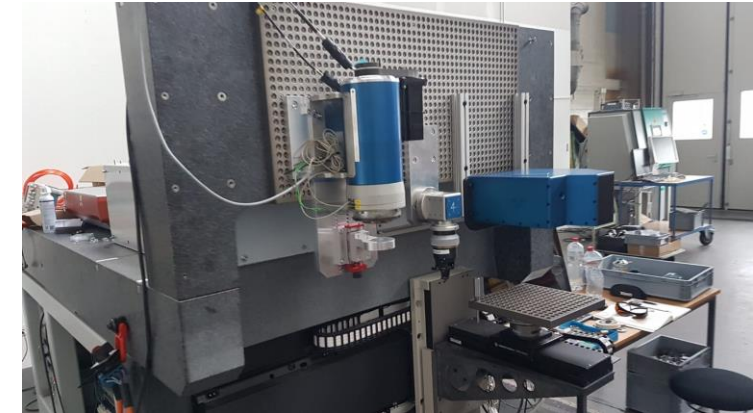
Example of an optimized Si ablation process

Laser / process parameters	Value	Unit
Average laser power	430	W
Pulse duration	320	fs
Intraburst distance	25	ns
Number of pulses per burst	7	
Scan velocity	15	m/s
Hatching distance	20	μm
Repetition rate	1280	kHz
Spot diameter	150	μm
Pulse energy per burst	336	μJ
Pulse energy	48	μJ
Energy specific ablated volume	4,32	mm ³ /kJ
Ablation rate	0,63	mm ³ /s
Surface roughness S_a	1,96	μm



Task 2.4: Upscaling of applications for high throughput - Diamond ablation

- Pre-work
 - Agreement between AMP, C4L and E6 for installation of industrial laser Tangor 100W
 - Follow up installation and integration according to E6 specifications
- Schedule of T2.4 for E6



WP 2 - Deliverables

Deliverable	Title	Due	Status	Comment
D2.1	Process limits 3D Si processing	M24 (01.2018)	Submitted	
D2.2	Process limits fine cutting of metal	M24 (01.2018)	Submitted	
D2.3	Process limits diamond processing	M24 (01.2018)	Submitted	
D2.4	Processing strategies for high power 3D Si processing	M30 (07.2018)	Submitted	Finalized M31.
D2.5	Processing strategies for high power fine cutting of metal	M30 (07.2018)	Delayed	Planned for M39
D2.6	Processing strategies for high power diamond processing	M30 (07.2018)	Delayed	Planned for M39

WP 2 - Milestones

Mile stone	Title	Due	Status	Comment
MS25	High quality 3D Si processing with low average power	M24 (01.2018)	Achieved	
MS26	High quality fine cutting of metal with low average power	M24 (01.2018)	Achieved	
MS27	High quality diamond processing with low average power	M24 (01.2018)	Achieved	
MS38	High quality 3D Si processing with high average power	M30 (07.2018)	Not achieved	Phase 1 (M22-M32): 450 W Phase 2 (later): 1000 W
MS39	High quality fine cutting of metal with high average power	M30 (07.2018)	Not achieved	Planned for M39
MS40	High quality diamond processing with high average power	M30 (07.2018)	Not achieved	Planned for M39